

Ahsanullah University of Science and Technology Department of Electrical and Electronic Engineering

LABORATORY MANUAL FOR ELECTRICAL AND ELECTRONIC SESSIONAL COURSES

Student Name : Student ID :

Course No. : **EEE 4134**Course Title : **VLSI-I Lab**

For the students of
Department of Electrical and Electronic Engineering

4th Year, 1st Semester

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Lab-1: Combinational Logic Circuit Design in Verilog HDL

Introduction

A hardware description language (HDL) is similar to a typical computer programming language except that an HDL is used to describe hardware rather than a program to be executed on a computer. Two HDLs are IEEE standards: Verilog HDL and VHDL (Very High Speed Integrated Circuit Hardware Description Language). Verilog language can be used in several ways to model digital systems. In this lab, we will implement combinational logic circuits using **Gate level or structural modeling**, **Data flow modeling (DFM)**, and **Behavioral modeling** styles of Verilog.

```
module module_name [(port_name{, port_name})];
    [parameter declarations]
    [input declarations]
    [output declarations]
    [inout declarations]
    [wire or tri declarations]
    [reg or integer declarations]
    [function or task declarations]
    [assign continuous assignments]
    [initial block]
    [always blocks]
    [gate instantiations]
    [module instantiations]
endmodule
```

Structure of a Verilog Module

Example 01

Example 01 demonstrates the Verilog HDL code of a Half Adder using the **Gate Level** abstraction.

```
module Half_Adder(s,c,x,y);
input x,y;

output s,c;

xor s1(s,x,y);
and c1(c,x,y);
endmodule
```

Example 02

Example 02 demonstrates the Verilog HDL code of a Half Adder using the **Data Flow** modeling style.

```
module Half_Adder(s,c,x,y);
input x,y;
output s,c;
assign s=x^y;
sassign c=x&y;
endmodule
```

Example 03

Example 03 demonstrates the Verilog HDL code of a 2X1 multiplexer using the **Gate Level** abstraction.

```
module mux_2to1(s,lo,l1,Y);
input s,lo,l1;
output Y;
wire w1,w2,w3;
not g1(w1,s);
and g2(w2,lo,w1);
and g3(w3,s,l1);
or g4(Y,w2,w3);
endmodule
```

Example 04

Example 04 demonstrates the Verilog HDL code of a 2X1 multiplexer using the **Data Flow** modeling style.

```
module mux_2to1(s,lo,l1,Y);
input s,lo,l1;
output Y;
assign Y=(~s& lo)|(s&l1);
endmodule
```

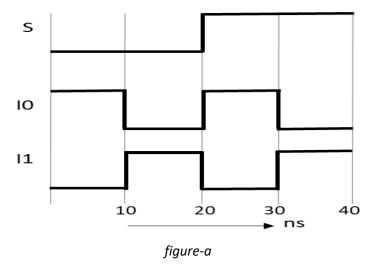
Example 05

Example 02 demonstrates the Verilog HDL code of a 2X1 multiplexer using the **Behavioral** modeling style.

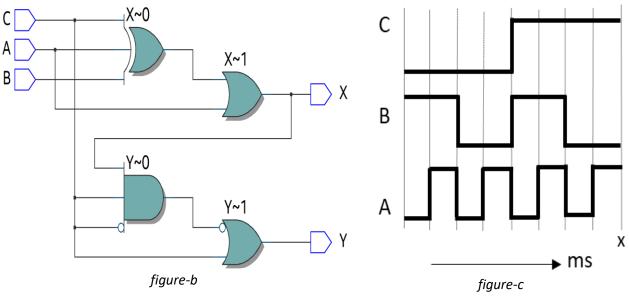
```
module mux_2to1(s,lo,l1,Y);
    input s,lo,l1;
    output reg Y;
     always@ (s,lo,l1) //if we use always @* The * operator will automatically identify all sensitive variables.
     begin
 6
             if(s==0)
 7
                     Y=Io;
 8
             else if(s==1)
 9
                     Y=I1;
10
             else
11
                     Y=0;
12
     end
     endmodule
```

Student Task

1. Verify the functionality of **Example-3** using the clock pulses shown in *figure-a*.



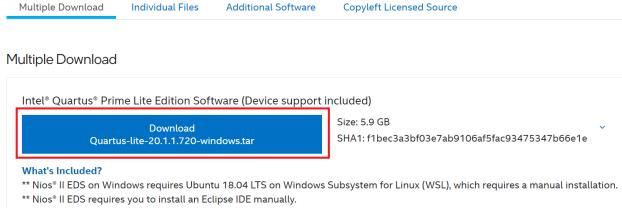
2. Write a Verilog code to obtain the same logic circuit of *figure-b* in **'RTL Viewer'** and verify the functionality of the circuit using the clock pulses shown in *figure-c*.



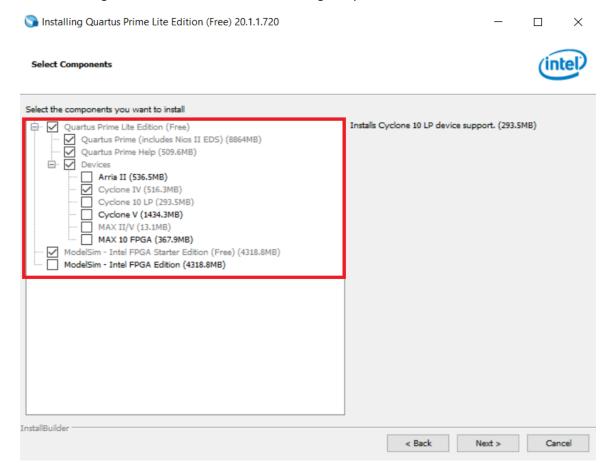
Installation of Quartus Prime

1. Download the Intel® Quartus® Prime Lite Edition Design Software Version 22.1.2 from the following link

https://www.intel.com/content/www/us/en/software-kit/660907/intel-quartus-prime-lite-edition-design-software-version-20-1-1-for-windows.html



- Extract the downloaded file.
- Run the setup.bat file.
- 4. During installation make sure the following components are selected.



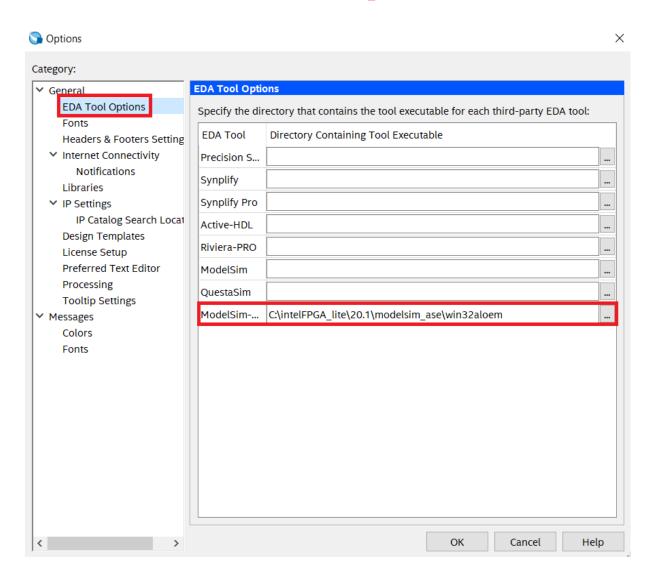
Simulating Verilog HDL using Quartus Prime

1. Find the following icon on your PC and run the software by double-clicking the icon.

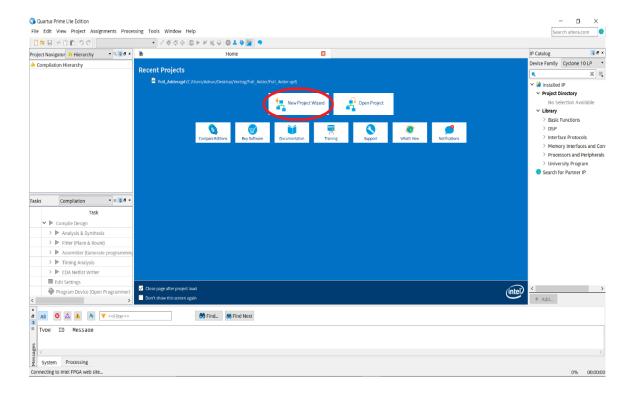


2. For using the Quartus Prime very first time we need to locate the directory of ModelSim Altera. For that execute **Tool** → **Options** → **EDA Tool Options** and give the proper location of ModelSim Altera and click **OK**. Normally the location is

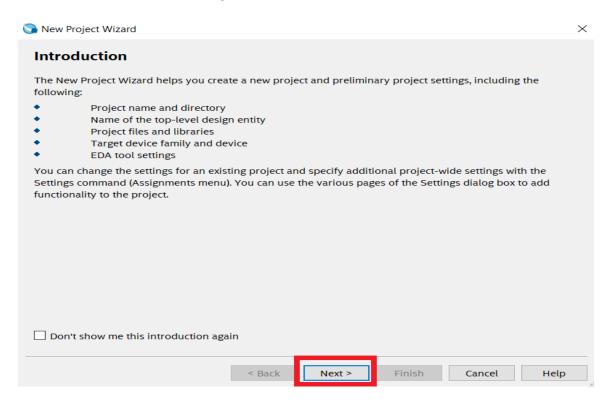
C:\intelFPGA_lite\20.1\modelsim_ase\win32aloem
or
C:\intelFPGA\20.1\modelsim_ase\win32aloem



3. The following window will pop up. Now click on the **New project wizard**.

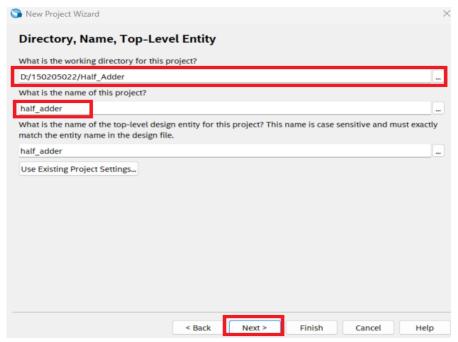


4. Click **Next** on the following window.

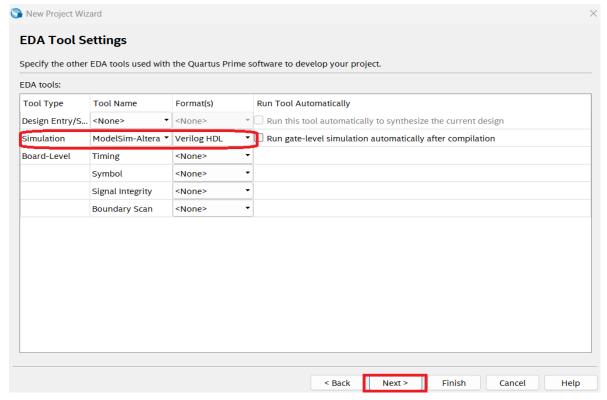


5. In the following window change the working directory of the project to your directory (e.g. D:\150205022/Half_Adder) and give a name to the project as shown and click **Next** four times.

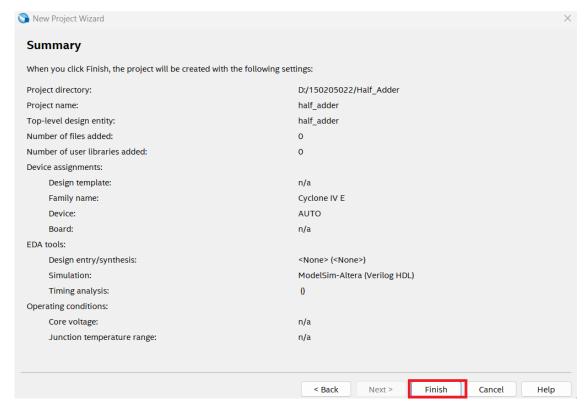
[Project name must be same as the top module]



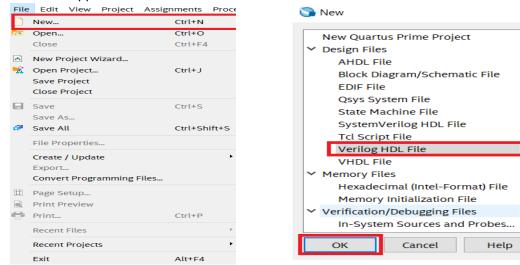
6. After clicking **Next** four times the following window will pop up then set the simulation tool as "Questa Intel FPGA", format as "Verilog HDL" and make sure the "Run gate-level simulation automatically after compilation" check box is not checked in the EDA tool settings window. After that click **Next.**



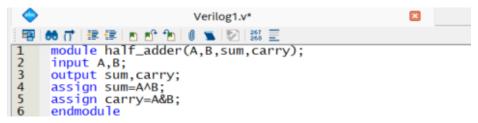
7. The summary window will appear and click **Finish.**



8. Execute File -> New. In the New window select the Verilog HDL file and click ok. The editor window will appear.



9. In the editor window write the Verilog module of your design.



Help

×

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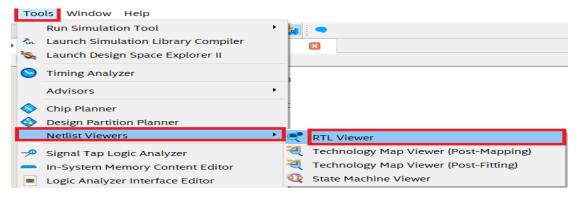
10. Now click on the compilation icon for compiling the design. In this step, the software will ask you to save the Verilog HDL file. Save it with the identical name of the project file.



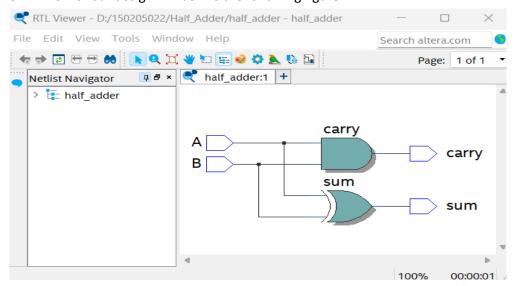
11. After successful compilation you will get the following message. Ignore the warnings.



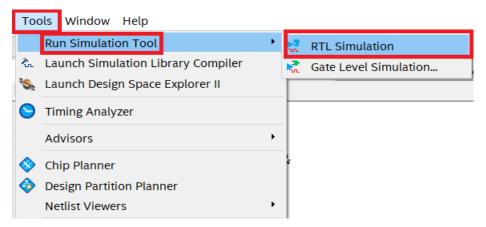
12. The RTL view of the Verilog module can be obtained in Quartus prime by executing **Tools** → **Netlist Viewers** → **RTL Viewer.**



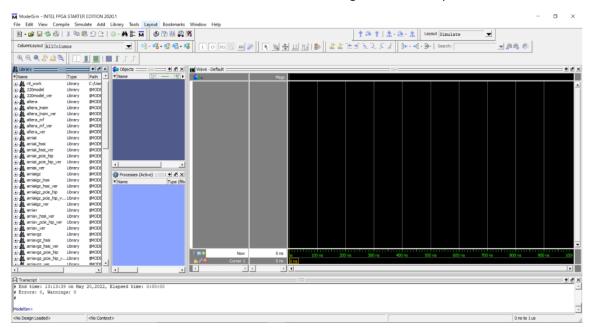
13. The RTL view of our design will be like the following figure.



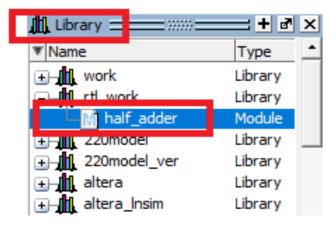
14. Now to launch ModelSim, execute **Tool** → **Run Simulation Tool** → **RTL Simulation**.



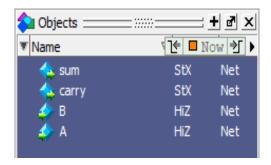
15. The ModelSim will be launched, and the following window will open.



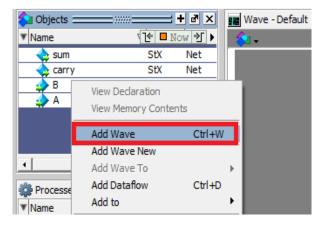
16. Now go to the **Library** window present on the left side of the ModelSim window and execute rtl_work→ <double click on your project module name>



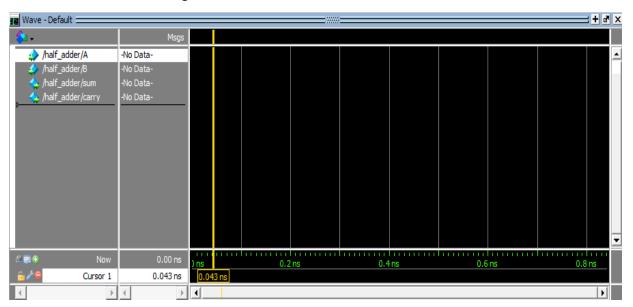
17. The input and output variables defined in the Verilog will appear in the **Objects** window.



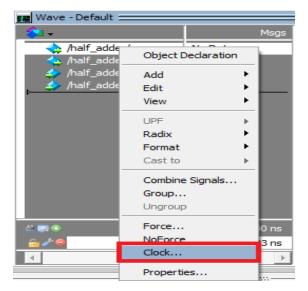
18. Now select all the input and output variables of the **Objects** window and by right-clicking on your mouse execute **Add Wave** to place them in the **Wave** window.



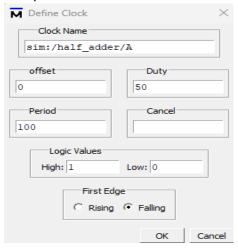
19. All the input and output variables will be placed on the **wave** window and the wave window will look like the following.



20. Now apply clocks to each input variable. Right-clicking any input variable and from the popped-up menu execute **Modify** → **Clock**.

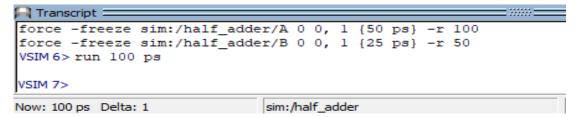


21. The **Define Clock** window will appear. Set parameters as per your requirement keep in mind all the units are in picoseconds by default.



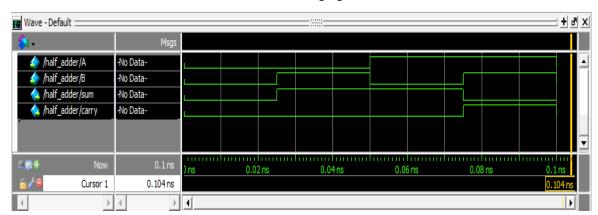
22. After defining all the input clocks, to evaluate the outputs write **run 100 ps** on the Transcript of ModelSim. Then the simulation will be performed for 100 ps.

[Give run length according to your requirement.]



Alternatively, we can run the wave output using the Run icon by typing the Run length





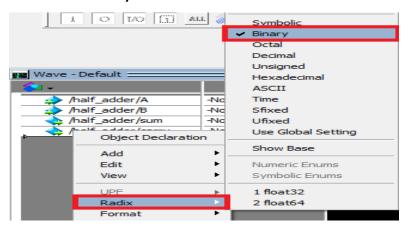
23. The wave window will look like the following figure after simulation.

If you need to change the clock pulse you must reset all the clocks before changing clocks otherwise the inputs and outputs will change after the previous run time which is not a convenient way to represent the inputs and outputs. The command "restart" is used in the transcript for resetting all the clocks. Alternatively, restart can be performed by executing Simulate -> Restart

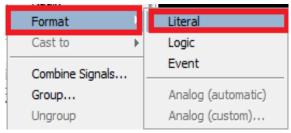
Showing Binary values on the Wave

Sometimes it is hard to verify the functionality of a digital system from the wave. For easy functional verification, we can read the binary values from the wave of ModelSim by doing the following steps.

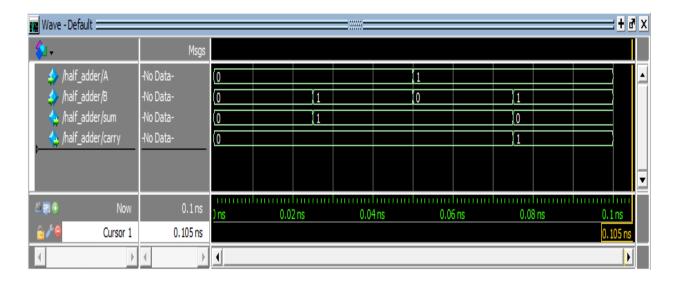
 Select all the input and output variables on the clock and right-click on the mouse and execute Radix → Binary.



II. After changing the **Radix**, change the **Format** type similarly by selecting all input and output variables on the wave by right-clicking on the mouse and then executing **Format**-> Literal.

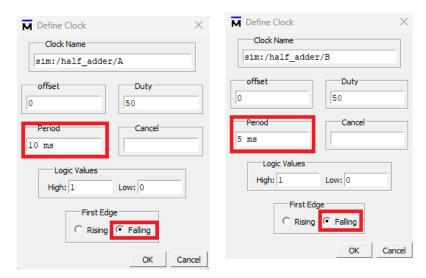


III. Now on the wave, binary values will be displayed which can be easily analyzed.

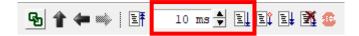


Changing Clock Unit

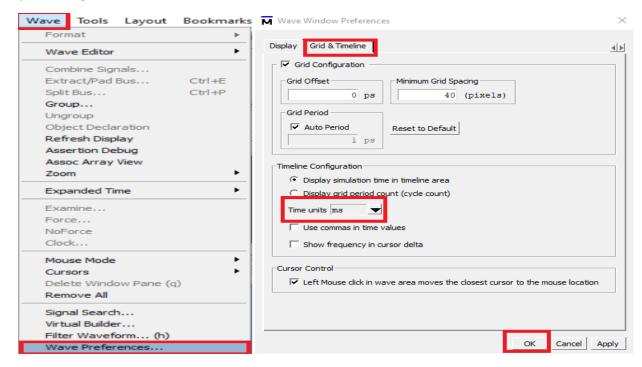
In step 21 it is mentioned that ModelSim's default timing unit is picosecond. But in some cases, we may need to define clocks in other units. Let us consider, that we need to define the period of a, b, and c as 10ms, 5ms, and 2.5ms respectively. Now define the clock a, b, and c as shown in the below figures.



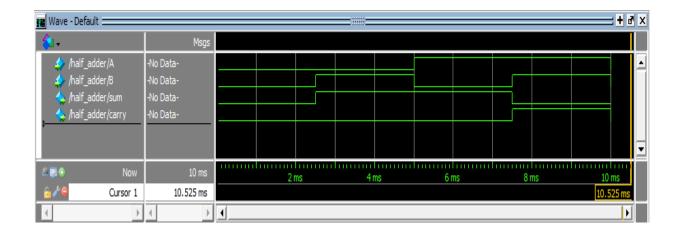
To view the output for all the input combinations the run length should be equal to the maximum period.



As all the units are in milliseconds, for easy visualization we can change the time units of the wave grid by executing Wave \rightarrow Wave Preferences \rightarrow Grid & Timeline \rightarrow Time units \rightarrow ms.



Now the ModelSim wave window will look like the following figure.



Similarly, for femtoseconds, nanoseconds, and microseconds, we can use fs, ns, and ms respectively

Lab-2: Digital System Design Using Verilog HDL

Example 01

Example 01 demonstrates the Verilog HDL code of a full adder following the **Hierarchical Modeling** style. In the design, a half-adder module is constructed from the predefined logic gates and then the half-adder module is used twice to design the full adder.

```
module Full_Adder(A,B,Cin,sum,carry); // Top module
 2
    input A,B,Cin;
    output sum, carry;
 4
    wire s1,c1,c2;
   Half_Adder sm1(s1,c1,A,B);
   Half Adder sm2(sum,c2,s1,Cin);
 7
    or o1(carry,c1,c2);
    endmodule
10 | module Half_Adder(s,c,x,y); // macro cell
11
    input x,y;
12
    output s,c;
13 | xor s1(s,x,y); // predefined primitive or leaf cells
14 and c1(c,x,y);
15 endmodule
```

N.B. One module can be instantiated to another module without maintaining the I/O sequence using the **Name Wise Instantiation** or **Explicit method** (.Exact_Port(Port_to_be_Assigned)).

Example 02

Example 02 demonstrates the Verilog HDL code of a 4 to 2 priority encoder with a valid bit.

```
module p encoder 4to2(D,Y,V);
 1
                       //declaring variable for input
    input [3:0]D;
    output reg [1:0]Y; //declaring variable for output
                    //declaring the variable for valid bit
    output reg V;
 5
    always@ *
    begin
 6
 7
            casex(D)
 8
                    4'b0001:
 9
                    begin
10
                            Y=2'b00; V=1;
                    end
11
12
                    4'b001x:
13
                    begin
                            Y=2'b01; V=1;
14
15
                    end
```

```
16
                   4'b01xx:
17
                   begin
18
                          Y=2'b10; V=1;
19
                   end
20
                   4'b1xxx:
21
                   begin
22
                          Y=2'b11; V=1;
23
                   end
24
                   default:
25
                   begin
26
                          Y=2'bx; V=0;
27
                   end
28
           endcase
29
    end
    endmodule
```

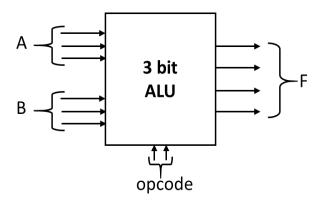
Example 03

Example 03 demonstrates the Verilog HDL code of a 2 to 4 decoder.

```
1 module decoder_2to4(s,e,y);
   input [1:0] s;
 3 | input e;
   output reg [3:0]y;
    integer k;
 6
    always@ (s,e)
 7
    begin
 8
            for (k=0;k<=3;k=k+1)
 9
                    begin
10
                    if ((s==k) && (e==1))
11
                           y[k]=1;
12
                    else
13
                           y[k]=0;
14
                    end
15
    end
16
    endmodule
```

Example 04

Example 04 demonstrates the Verilog HDL code of a 3-bit arithmetic logic unit that works according to the function table mentioned in *Table-1*



Block representation of the ALU of Example 04

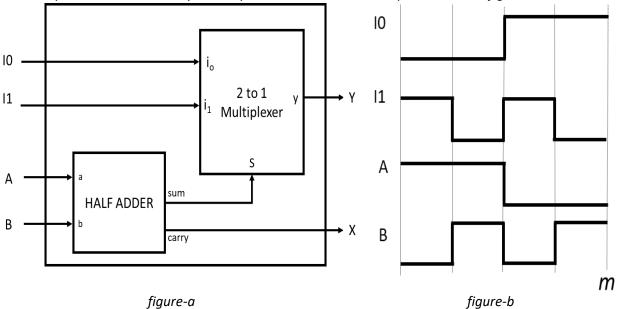
Table-1

Operation Code	Function
00	Binary sum of A and B
01	Adds 1 with B
10	2s complement of A
11	Bitwise XOR operation between A and B

```
module ALU_4bit(A,B,F,opcode);
 2
   input [2:0]A, B;
 3 input [1:0]opcode;
    output reg [3:0]F;
 5
    always@ (*)
    begin
    case(opcode)
 8
            2'b00:F=A+B;
 9
            2'b01:F=B+1;
10
            2'b10: F=-A;
11
            2'b11: F=A^B;
12
            default:F=0;
13
    endcase
14
    end
15
    endmodule
```

Student Task:

1. Write a Verilog code to implement the system shown in *figure-a* using two submodules and a top module. Hence verify the output X and Y with the clock pulse shown in *figure-b*.



- 2. Write a Verilog code to implement a 4x1 Multiplexer with the minimum number of 2x1 Multiplexers.
- 3. Write a Verilog code to implement a BCD adder using behavioral statements.
- 4. Write a Verilog code to implement a 4-bit magnitude comparator.
- 5. Write a Verilog code to implement a 4-bit ripple carry adder using full adders.

Lab-3: Sequential System Design Using Verilog HDL

Example 01

Example 01 demonstrates the Verilog HDL code of a SR Latch

```
module sr_latch(s,r,Q,clk);
 2
    input clk,s,r;
    output reg Q;
    always@ *
 5
    begin
    if(clk==1)
 7
            begin
 8
                     case ({s,r})
 9
                     2'b00:Q=Q;
10
                     2'b01:Q=0;
                     2'b10:Q=1;
11
12
                     default:Q=1'bx;
13
                     endcase
14
             end
15
    end
16
    endmodule
```

Example 02

Example 02 demonstrates the Verilog HDL code of a JK Latch.

```
module jk_latch(J,K,Q,clk);
 2
    input clk,J,K;
    output reg Q;
 4
    always@ (*)
 5
    begin
 6
            if(clk==1)
 7
            begin
 8
            case({J,K})
 9
                     2'b00:Q=Q;
10
                     2'b01:Q=0;
11
                     2'b10:Q=1;
12
                     2'b11:Q=~Q;
13
                     default:Q=1'bx;
14
            endcase
15
            end
    end
16
17
    endmodule
```

Example 03

Example 03 demonstrates the Verilog HDL code of a D Latch using behavioral statements.

```
module D_latch(D,Q,clk);
input clk,D;
output reg Q;
always@ (*)
begin
if (clk==1)
Q=D;
end
endmodule
```

Example 04

Example 04 demonstrates the Verilog HDL code of a T Latch using behavioral statements.

```
module T_latch(T,Q,clk);
 2
    input T,clk;
 3
    output reg Q;
    always@ (*)
 5
    begin
 6
            if (clk==1)
 7
            begin
 8
                    if(T==0)
 9
                             Q=Q;
10
                     else if(T==1)
11
                             Q=~Q;
12
            end
13
    end
14
    endmodule
```

Example 05

Example 05 demonstrates the Verilog HDL code of a positive edge triggered D flip-flop.

```
module D_FF(clk, D,Q);
input D,clk;
output reg Q;
always@(posedge clk)
Q=D;
endmodule
```

Example 06

Example 06 demonstrates the Verilog HDL code of a positive edge triggered D flip-flop with synchronous set and reset.

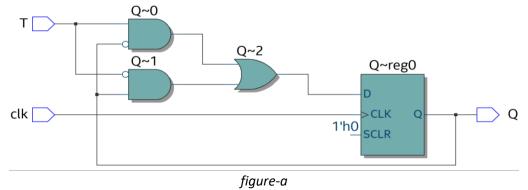
```
1
    module D_FF(clk, rst, set, D, Q);
 2
    input D,set,rst,clk;
 3
    output reg Q;
    always@ (posedge clk)
 5
    begin
 6
             if(rst==1)
 7
                     Q=0;
 8
             else if(set==1)
 9
                     Q=1;
10
             else
11
                     Q=D;
12
    end
13
    endmodule
```

Example 07

Example 07 demonstrates the Verilog HDL code of a positive edge triggered D flip-flop with asynchronous reset.

```
module D_FF(clk, rst, set, D, Q);
    input D,set,rst,clk;
 3
    output reg Q;
 4
    always@ (posedge clk, posedge rst)
 5
    begin
 6
             if(rst==1)
 7
                     Q=0;
 8
             else if(set==1)
 9
                     Q=1;
10
             else
11
                     Q=D;
12
    end
13
    endmodule
```

Example 08



Example 08 demonstrates the Verilog HDL code of the RTL view shown in figure-a.

```
module rtl1(T,clk,Q);
input T,clk;
output reg Q;
always@(posedge clk)
begin
Q<=(T&(~Q))|(Q&(~T));
end
endmodule
```

Example 09

Example 09 demonstrates the Verilog HDL code of a 2-bit up counter with synchronous enable.

```
module up_count(clk,E,Q);
input clk,E;
output reg [1:0]Q;
always@(posedge clk)
if(!E)
Q=0;
else
Q=Q+1;
endmodule
```

Example 10

Example 10 demonstrates the Verilog HDL code of a 4-bit shift registrar.

```
module shift_reg(w,clk,Q);
 2
    input w,clk;
    output reg [3:0]Q;
    always@(posedge clk)
 5
    begin
 6
             Q[3] <= w;
 7
             Q[2] <= Q[3];
 8
             Q[1] <= Q[2];
 9
             Q[0] <= Q[1];
10
    end
11
    endmodule
```

Student Task

1. Verify the functionality of **Example-09** using the clock pulses shown in *figure-a*.

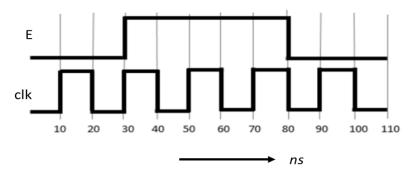


figure-a

2. Write a Verilog code to obtain the same logic circuit of *figure-b* in **'RTL Viewer'**.

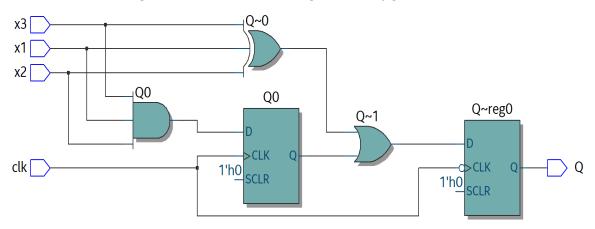
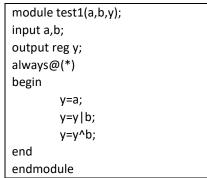
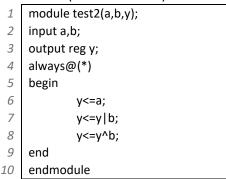


figure-b

3. What is the difference between the outputs of the two modules (test1 and test2) shown below?





- 4. Write a Verilog code to design a BCD counter.
- 5. Write Verilog code for a universal shift register which can shift left/right and can load data both in parallel mode and serial mode.
- 6. Write the Verilog code for a logic circuit which counts to 3 if selection input (composed of 2 bits) $S_1S_0 = 01$, counts to 7 if $S_1S_0 = 10$, counts to 15 if $S_1S_0 = 11$. If $S_1S_0 = 00$, then it halts counting. Use positive edge-triggered counter.

Lab-4: CMOS Inverter Design Using Cadence Virtuoso

Objectives:

- To learn how to logging into the Cadence Virtuoso.
- To learn how to draw schematic of basic logic gates in Cadence Virtuoso.
- To learn how to create symbol view from schematic view

Steps to Login into the server



The detailed instructions are given below

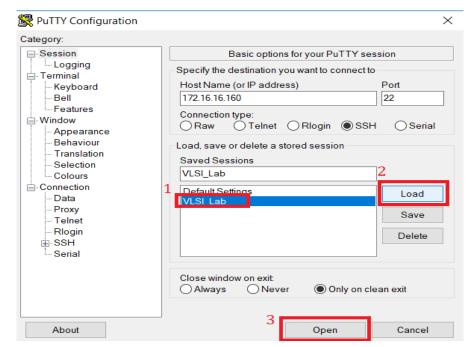
1. Find the Desktop shortcut icon for **XLaunch**. Double-click on it. Click **Next, Next, Next, Finish** (in that order) in the windows that pop up one after another.



After it starts, you will see the Xming icon at the bottom right corner of your Desktop screen.



2. Find the icon for Putty. Double click on it to open it. 'Putty Configuration' window will pop-up



3. Select VLSI_LAB under the 'Saved Sessions' category. Click Load and then click Open.

4. Now you will see a Terminal window which prompts you for login.



5. Log in to your workstation using your username and password. Your username will be eee_<student id> and your password will be your student ID. When you are typing your password, the command window will not display the characters you type in, so make sure you are typing the right password. After logging in to your account, the terminal window should look like the following:

6. Type **csh** and press the 'Enter' key.

```
eee_150205105@aust:~ - \ \X

login as: eee_150205105

eee_150205105@172.16.16.160's password:

Last login: Sun Dec 10 15:19:39 2023 from 172.16.16.166

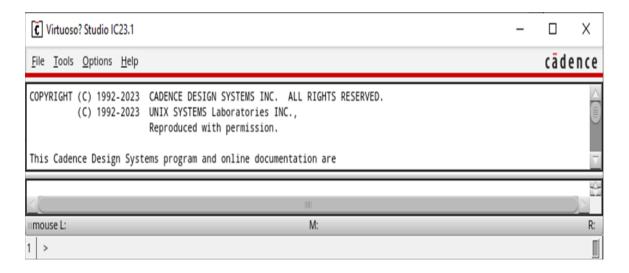
[eee 150205105@aust ~]$ csh
```

7. Then type **source cshrc_q** and press the **'Enter'** key. The following message will be displayed in the Terminal window: Welcome to Cadence Tools That means you can use Cadence tools now.



[eee_150205105@aust ~] \$ virtuoso &

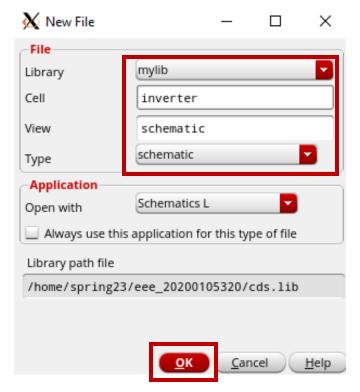
9. Virtuoso® **Command Interpreter Window (CIW)** appears at the bottom of the screen. From the CIW menus, all Cadence main tools, online help and options can be accessed. In the window area, all kind of messages (info, errors, warnings, etc) generated by the different Cadence tools appear. You can also introduce commands.



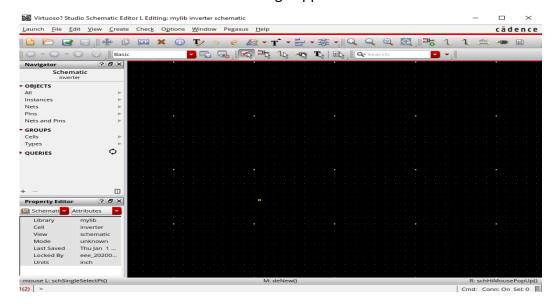
Creating a Schematic

1. In the Command Interpreter Window (CIW), execute File →New →Cellview. Set up the 'New File' form as follows:

Library: *mylib*, **Cell:** *inverter*, **View:** *schematic*, **Type:** *schematic*, **Application: Open with:** *Schematics L*



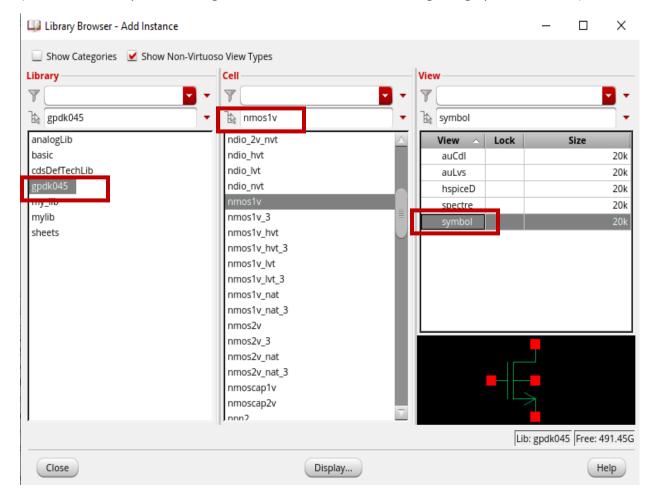
A blank schematic window for the inverter design appears.

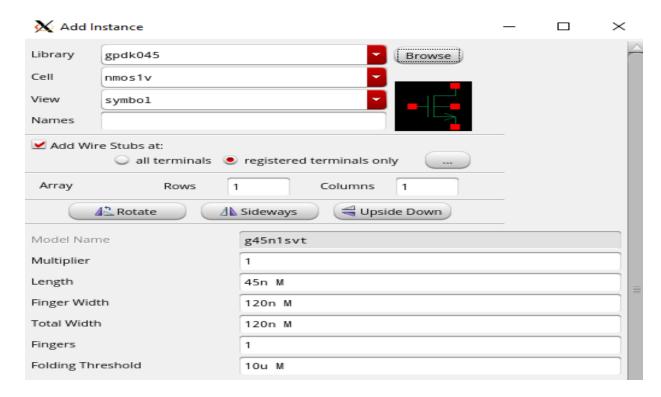


2. To create an instance, you can execute *Create → Instance* in Virtuoso schematic editor window or simply use shortcut key "i". The following window will appear. Click **Browse** to select a library component.

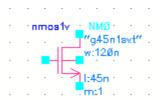


3. Library Browser window will show up. Choose **Library**: *gpdk045*, **Cell**: *nmos1v*, **View**: *symbol*. (Note that while you are doing this, the 'Add Instance' form is getting updated as well).





4. Make sure that the *view* name field in the form is set to *symbol*. After you complete the form, move your cursor to the schematic window and click left button of mouse to place the component. After entering the components, click **Cancel** in the **Create Instance** form or press **Esc** keeping your cursor in the schematic window.



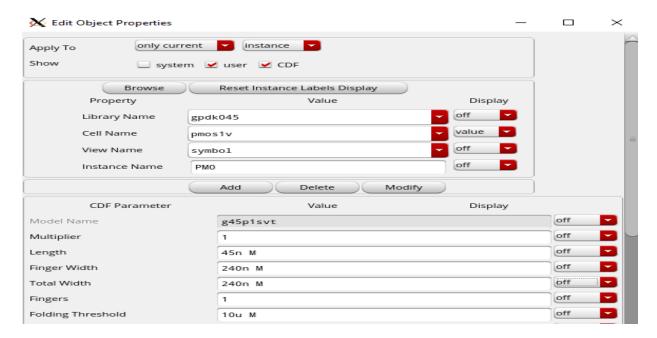
Similarly, add pmos1v cell.

If you place component in the wrong location, press 'm' on keyboard, click once on the component to select it and move the mouse to move the component to your desired location.

5. Now we can adjust the sizes of the transistors by editing instance properties. Left click on the NMOS to select the component. Then, press " \mathbf{q} " to modify its properties, or in schematic editor window, execute $\mathbf{Edit} \Rightarrow \mathbf{Properties} \Rightarrow \mathbf{Object}$.

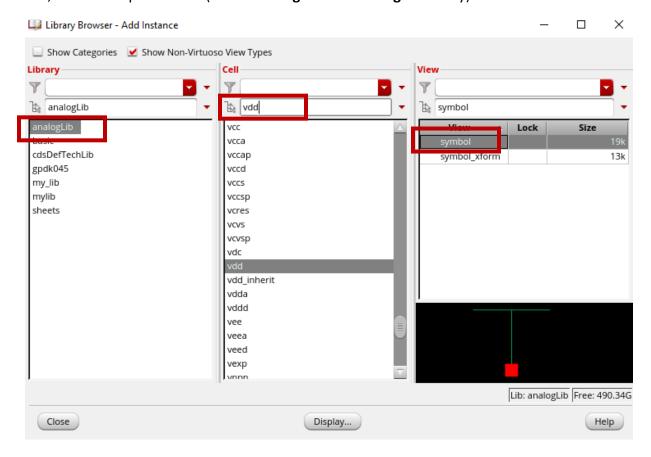
You will update the Library Name, Cell Name, and the property values given in the table below as you place each component. The inverter design contains the following cells from the following libraries.

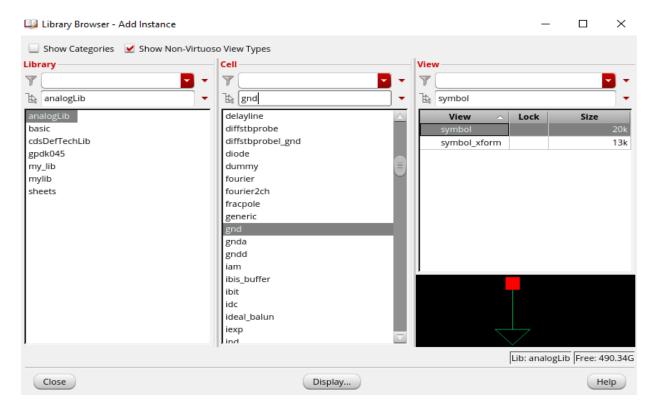
For example, while modifying the transistor width for PMOS, set **Total Width** to 240n, and then press '**Tab**' key and the **Finger Width** will be set to the same value. Click **OK**.



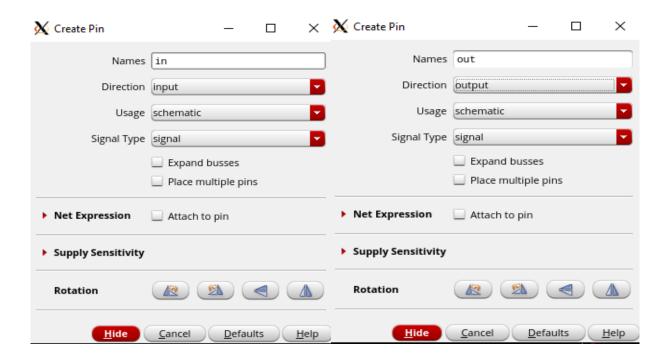
To deselect any object, press keyboard command "Ctrl+d".

Next, instantiate power nets (cell vdd and gnd from analogLib library).





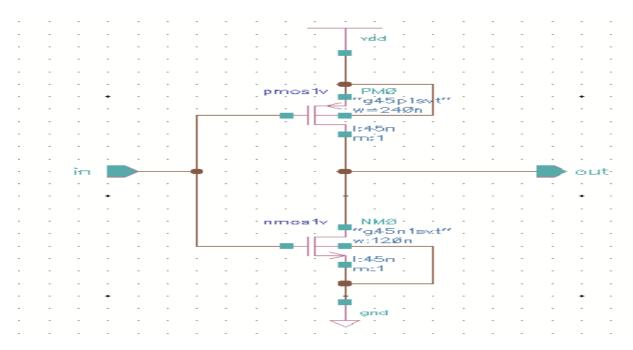
6. Execute *Create* → *Pin* or press 'p' on keyboard. 'Add Pin' form will appear. Enter the name of the pin and **Direction** of the pin. Add all the pins (in, out) to the schematic. For an inverter, gate input pin (e.g. in) is the input and output pin (e.g. out) at the common node between drains of NMOS and PMOS is output of the inverter. So, select **Direction** property as input for in, and output for out.



7. Use Add → Wire menu or simply press 'w' key while staying on the schematic editor to enter wiring mode / Esc to exit. Click and release left button of mouse to start wire connections and click again at another point to draw wire connection.

It is a good practice to periodically save your work by clicking on **Check and Save** button (the checkmark button just below the Tools menu). You can also save your work from the drop-down menu **File ->Save**.

The final schematic looks like the following one:



8. Click Check and Save.



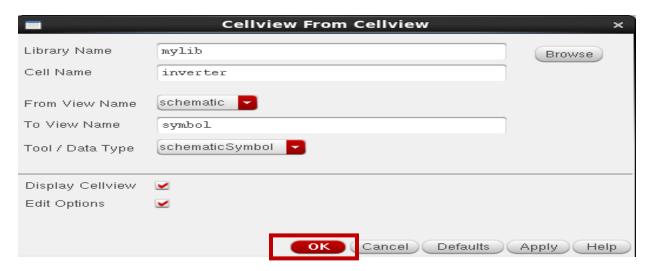
9. Check **CIW** for errors or warnings. Some licence warnings may be ignored. If there are no error or design warning, you should see the following message:

```
INFO (SCH-1183): No changes were made. No objects updated.
INFO (SCH-1170): Extracting "inverter schematic"
INFO (SCH-1426): Schematic check completed with no errors.
INFO (SCH-1181): "mylib inverter schematic" saved.
```

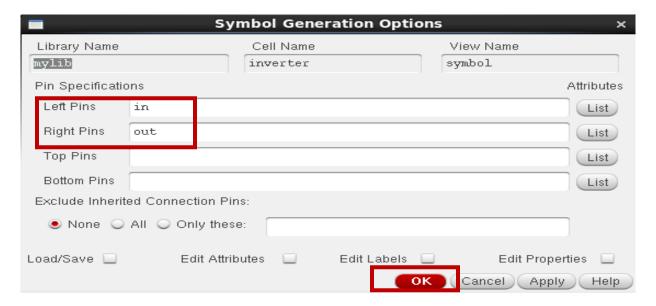
Symbol Creation

We will create a symbol for your inverter design so that we can use this symbol view for the schematic in a hierarchical design.

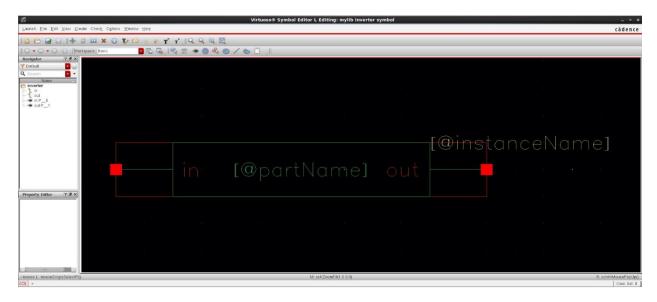
1. In the schematic editor window for *inverter*, execute *Create* → *Cellview* → *From Cellview*. 'Cellview from cellview' window appears. Click OK.



2. In the 'Symbol Generation Options' window, you can choose the location of the pins.



3. Click **OK** on the 'Symbol Generation Options' window and the Symbol Editor window will open.



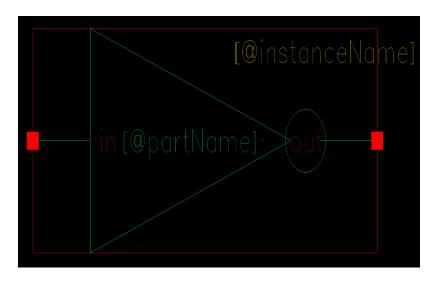
3. Click **Delete** icon in the symbol window, delete the outer red rectangle and green rectangle.



- **4.** Execute *Create* → *Shape* → *polygon*, and draw a shape similar to triangle. After creating the triangle, press Esc key.
- **5.** Execute *Create* \rightarrow *Shape* \rightarrow *Circle* to make a circle at the end of the triangle. You can move the pin names according to the location.
- **6.** Execute *Create* → *Selection Box*. In the 'Add Selection Box' form, click 'Automatic'. A new red selection box is automatically added.



7. After creating symbol, click on the save icon in the symbol editor window to save the symbol. In the symbol editor window, execute *File →Check and Save*. Then close the symbol editor window.



Appendix: Cadence Virtuoso® Schematic Editor L Shortcuts

Shortcut key	Tasks performed
W	Add a wire
i	Add an instance
p	Add a pin
1	Add label to a wire
e	Display options
q	Select an object and press q to open 'Edit
	Object Property' dialogue box
]	Zoom out
]	Zoom in
c	Сору
m	Move
u	Undo
Shift+u	Redo
f	Fit the entire schematic in the window

Student Task

7. Implement 3 input NOR and NAND gate using CMOS logic family

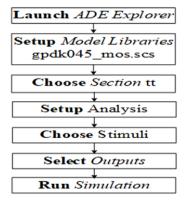
Lab-5: Measuring Different Performance Parameters of a CMOS Inverter

Objectives:

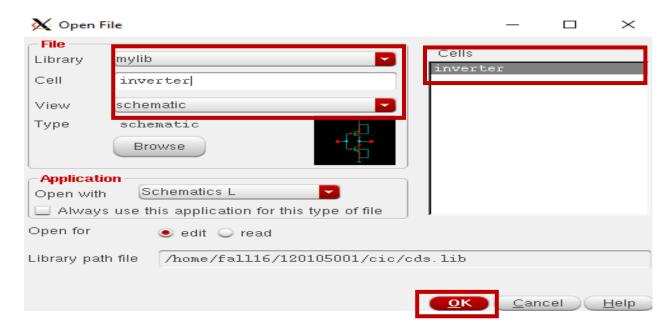
- To verify the functionality through transient simulation.
- To measure power dissipation, propagation delay, rise time and fall time of logic gates.
- To learn about process corners and their effects on delay and power dissipation

Functional Verification

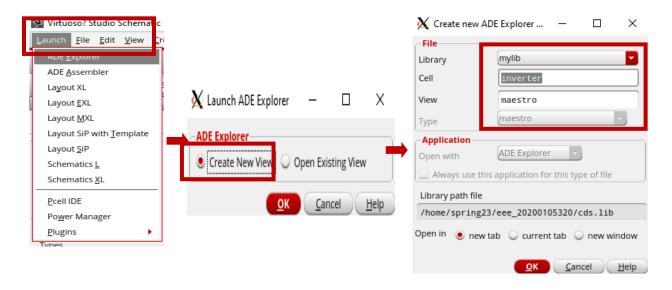
The following flowchart shows the steps to be executed to simulate a design using ADE Explorer:



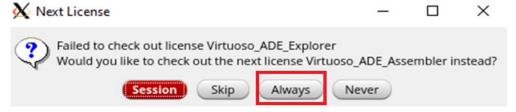
1. To simulate the schematic of inverter first open the schematic of inverter, execute *File* → *Open* in CIW. In the 'Open File' window, select the inverter schematic from the list. Click OK.



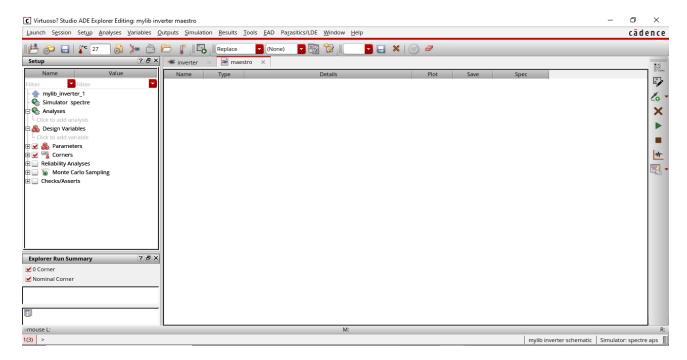
2. In the Schematic editor window, execute *Launch* → *ADE Explorer*. The following window may appear.



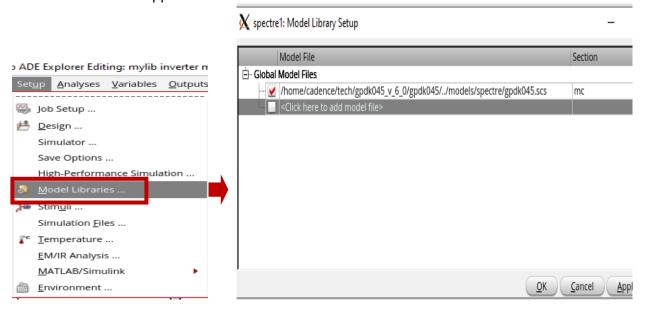
The following window may appear. Click Always.



Analog Design Environment (ADE) Explorer window will appear.



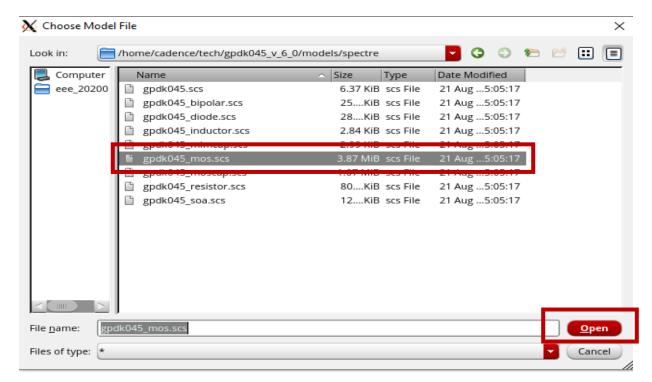
6. Set up the model libraries by executing **Setup** →**Model Libraries**. '**Model Library Setup**' Window will appear:



Click twice on the file name given under Global Model Files. An ash coloured button will appear.

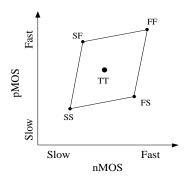


Click on the button. 'Choose Model File' window will appear.



8. Select **gpdk045_mos.scs** from the list. Click **Open**.

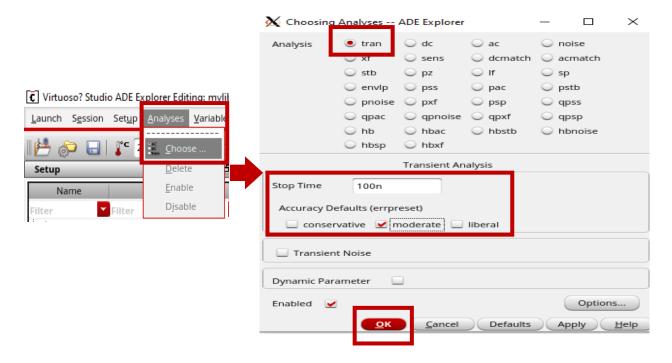
In this model file, there are models to simulate various corners like fast-fast (FF), fast-slow (FS), typical-typical (TT) etc. These are called process corners, depending on the speed of MOS transistors (NMOS and PMOS). Refer to the following figure for the definition of process corners:

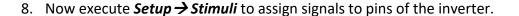


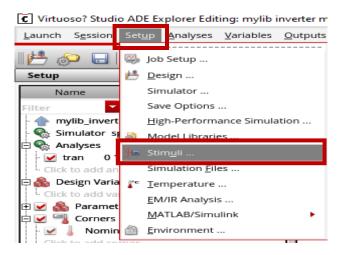
We will choose the section typical from the **Section** scroll bar and select the section 'tt'. These will enable us to use the TT models of the 1.2 V MOS transistors. Only one **Global Model File** will be defined. Uncheck or delete any other model files that appear. Click **OK**.



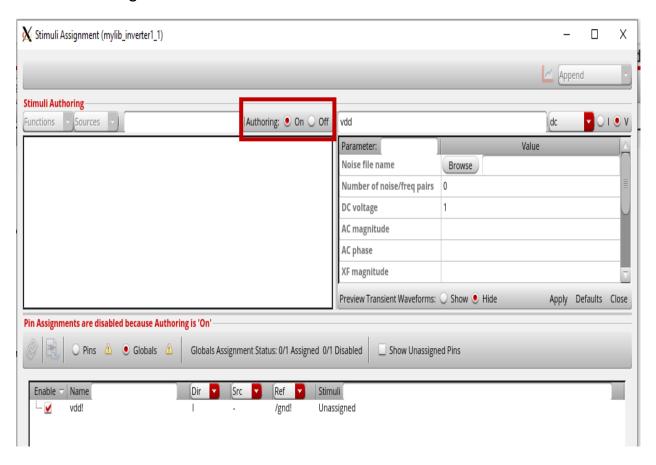
Now choose the analysis to be done from Analyses → Choose. Select transient (tran) analysis to be done. Provide a reasonable value for 'stop time' to observe few periods of signals. (e.g. Analysis: tran, Stop Time: 100n, Accuracy Defaults: moderate). Click OK.



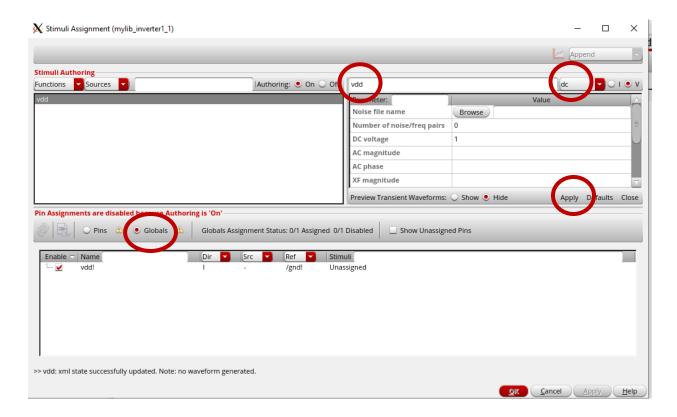




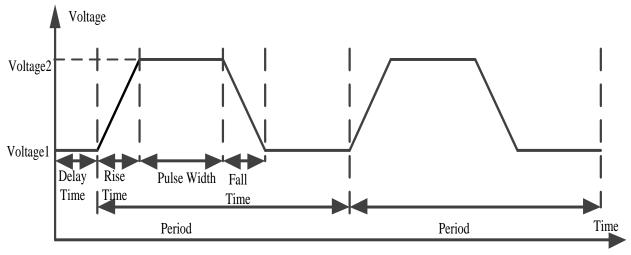
8. In 'Stimuli Assignment' window, select Globals. Now you can see global power net vdd!. Click on Authoring → ON.



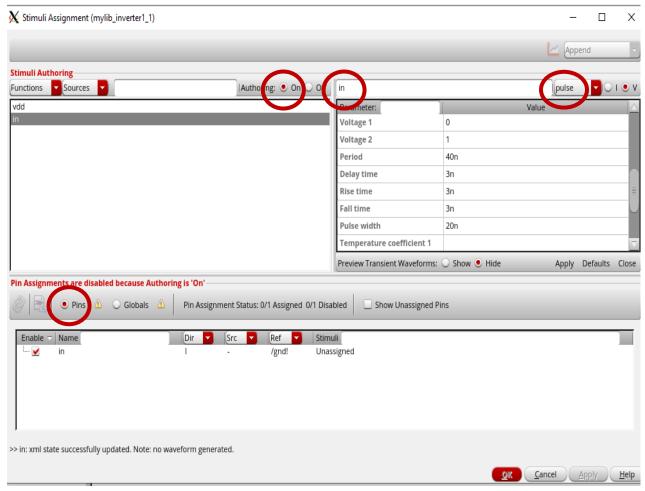
Write **vdd** in the box and select **dc** under the drop down menu. Put a value of 1 on the **DC voltage** box. The filled up form for '**vdd!**' will look like the one below. Click **Apply** (clicking **OK** will close the window and it will have to be reopened to setup inputs).



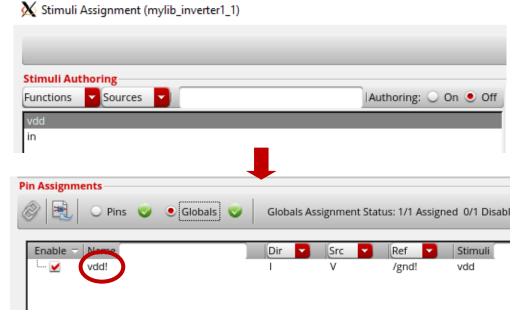
9. Select **Inputs**. For input pin '**in**', we have to set a pulse waveform. The following figure shows the definition of pulse parameters:



For setting signal to input pin 'in', select **Pins** in **Stimuli Assignment** window. Click on **Authoring ON**, write **in** in the box and select 'pulse' under the drop down menu. Parameters for pulse source will be as follows: **Voltage1** = 0V, **Voltage2** = 1V, **Period** = 40n, **Delay time** = 3n, **Rise time** = 3n, **Fall time** = 3n, **Pulse width** = 20n. Click **Apply** and then click **OK**. (Delay, Rise time and Fall time can also be set at ps ranges for sharp transitions).

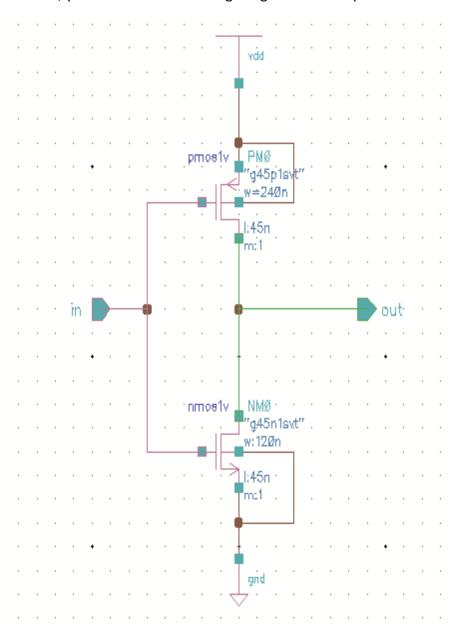


10. Now Click on **Authoring** → **OFF.** Then select the pin **vdd** in the **Stimuli Authoring window**. Go to **Pin Assignments** → **Right Click on vdd!** → **Assign Stimuli to selected Pin.**

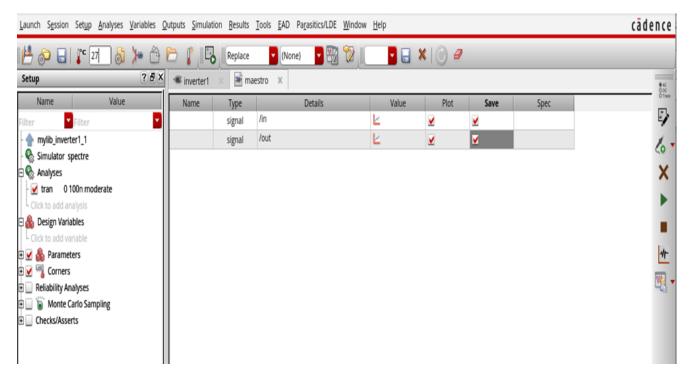


Do the same for other pins that has been defined previously.

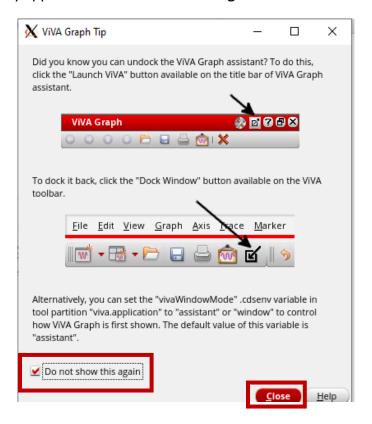
10. Select the output to be plotted by executing *Outputs →To be plotted →Select on Design* in the ADE window. Schematic editor window will pop up, select 'out' and 'in' by clicking on the pins/terminals or selecting from the list on the left hand side as shown in the figure below. When you select them, you will see colours being assigned to these pins.



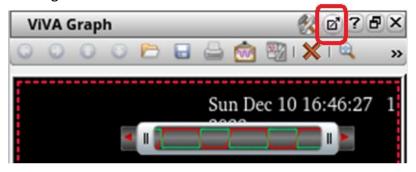




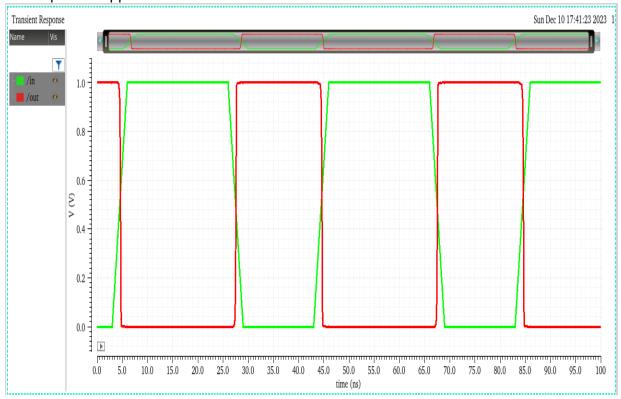
12. Now run the simulation by executing *Simulation* → *Netlist and Run* in the ADE window. The following window may appear. Click on **Do not show again** → **Close.**



The simulation will run and the VIVA Graph will appear in window as shown below. Click on the marked icon shown in figure.

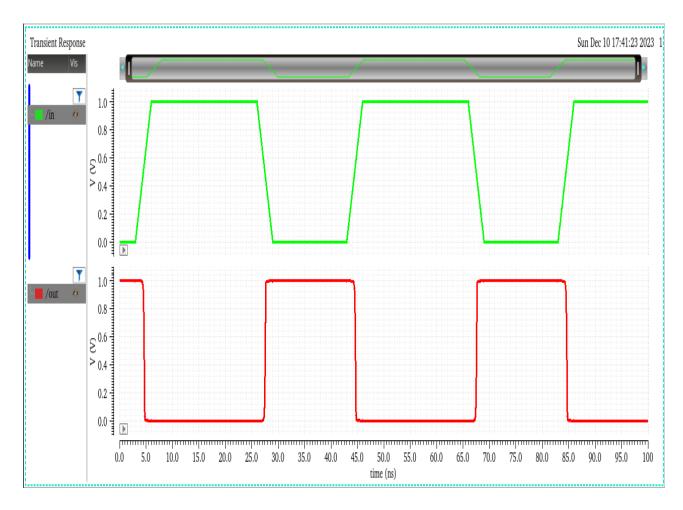


The output will appear in virtuoso visualization window as shown below.



13. Finally, we are going to separate the plots into two sub-graphs. Click on the following icon for splitting graphs.





The final plot should look like the one shown below:

Measuring average power using Waveform calculator

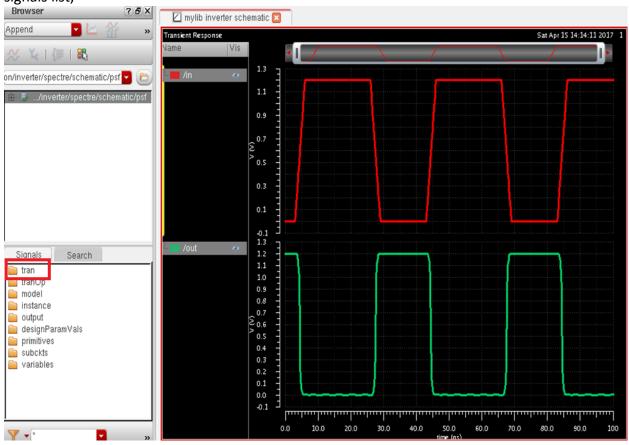
We will compute the average power consumed in a circuit for the duration of transient simulation window.

1. To do this, make sure that before running simulation you select the *Outputs →Save All* option in ADE L window. 'Save Options' window will appear. Under 'Select power signals to output (pwr)' option, put a tick mark in all option. Click OK.



2. Then simulate the circuit as usual, by executing **Simulation** →**Netlist and Run**.

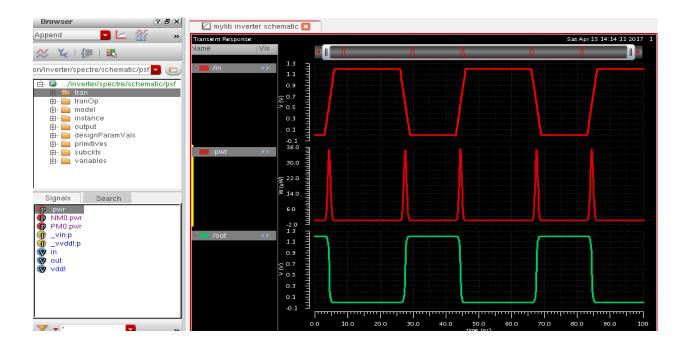
Execute *Tools* \rightarrow *Result Browser* in ADE L window. 'Result Browser' window will appear to the left side in 'Virtuoso Analysis and Visualization XL' window. Double-click on tran. From the signals list,



3. Now double-click on :pwr



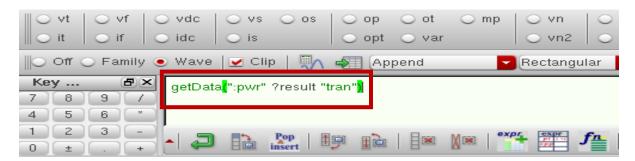
4. The waveform display window will show the ":pwr" (the instantaneous power consumed by the whole circuit) along with 'in' and 'out' signals.



5. Now, open **Waveform calculator** window. The calculator window appears. Make sure the "**Wave**" and "**Clip**" options are selected.



6. Now switch back to the waveform window and left click the mouse once on the power waveform. Then switch back to the calculator window. The buffer window should be filled in as follows:



7. Now select 'average' from 'Special Functions' Menu and click apply.



8. The buffer will now look like the following one:



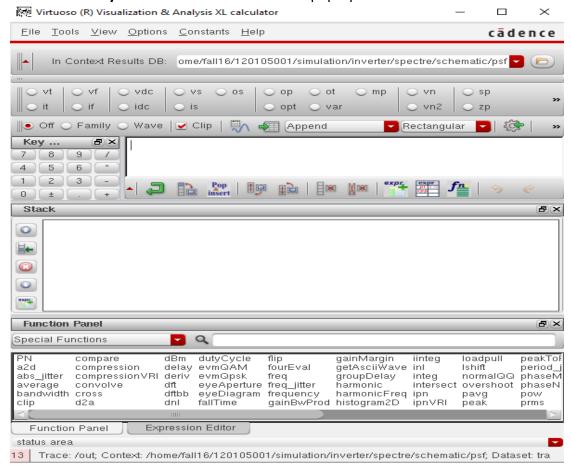
9. Click on **Evaluate the buffer** icon and the average power dissipation in that time window will be displayed (about 1.838 μ W in this example).



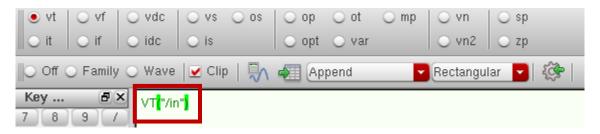
Measuring propagation delay using Waveform calculator

Waveform calculator can be used to perform many different measurements and transformations on the waveforms displayed in the waveform window. This includes – computing the average of a waveform (e.g. power) over the entire length of the simulation or in a given period of time, finding the propagation delay of between input and output signals, or addition/subtraction/multiplication/division of waveforms, etc.

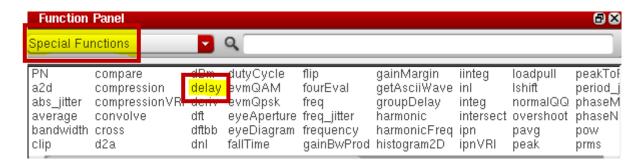
1. Execute *Tools* — Calculator in Virtuoso Visualization & Analysis XL window. 'Virtuoso Visualization & Analysis XL calculator' window will pop-up:



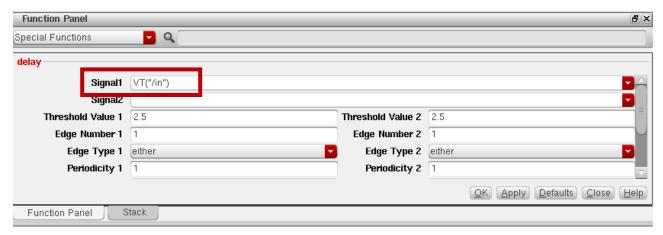
2. Select 'vt'. Go to Schematic editor window and click on input node 'in'. An expression (e.g. VT("/in")) will appear. Copy the expression.



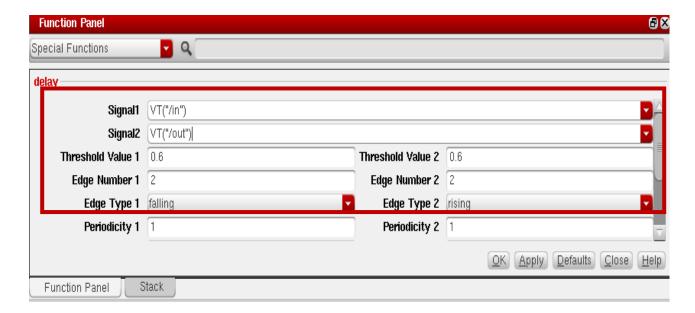
3. In the Function Panel, select 'Special functions' and select 'delay'.



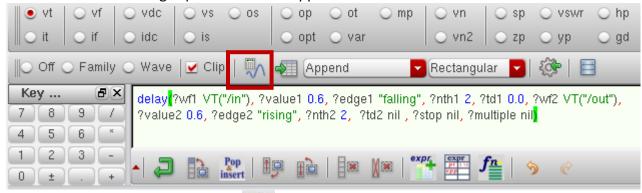
4. The following window will appear. Put the expression previously obtained in the field 'Signal1'. Do the same for output signal 'out' to fill in the field 'Signal2'.



Fill up the rest of the form as follows:

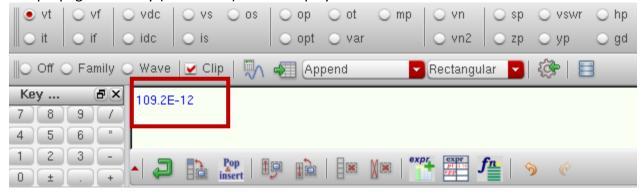


5.Click **OK**. The following expression should appear:



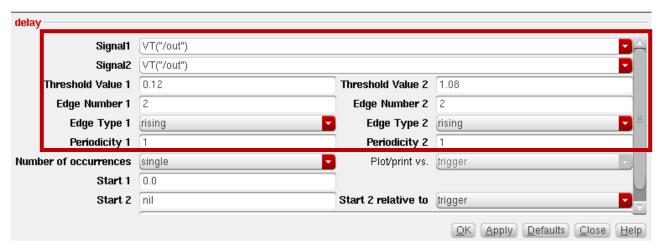
6. Click on **Evaluate the buffer** icon.

The propagation delay (in seconds) will be displayed in the window.

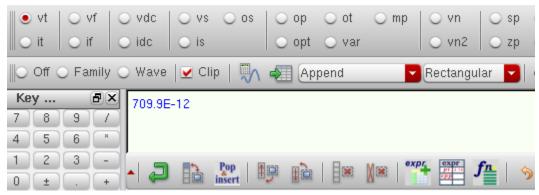


Measuring rise time and fall time using Waveform calculator

- **1.** Open the 'delay' function window under **Waveform calculator** in the same way that you followed for propagation delay measurement. This time both **Signal1** and **Signal2** will be **VT("/out")**.
- **2.** Threshold value 1 and 2 should be **0.12** (10% of 1.2 V supply) and **1.08** (90% of 1.2 V supply) respectively for 10% to 90% rise time calculation. These values should be swapped for fall time calculation.
- **3.** For rise time/fall time calculation, both the **Edge numbers** must be the same.
- **4.** The **Edge type**s should be rising for rise time calculation and falling for fall time calculation. *Example:* Rise time calculation of rising edge 2 for an inverter:



5. Click **OK** after filling in the form as shown above. The following expression should appear:



Student Task

- 1. Explain the nature of power consumption curve.
- 2. Perform SS, FF, SF and FS process corner simulations and compare the power consumption and propagation delays.

Lab-6: DC Sweep and Parametric Sweep in Cadence Virtuoso

Objectives:

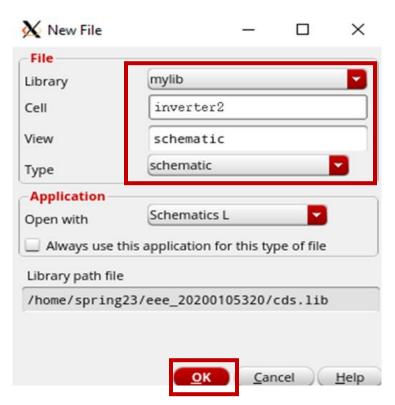
- To learn how to perform DC sweep and parametric simulation.
- To learn the voltage transfer characteristics of inverter.

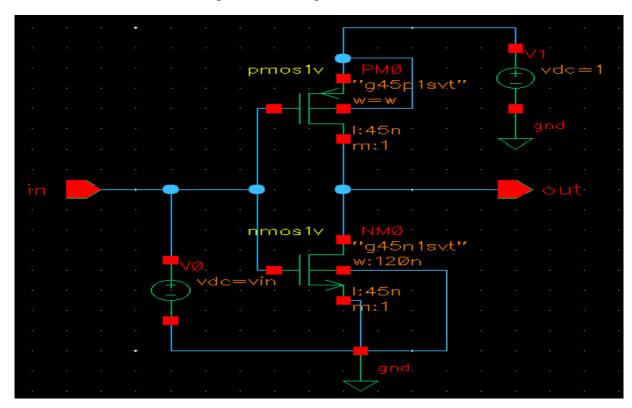
Obtain the voltage transfer characteristics of inverter

We will perform both DC and parametric simulation at the same time on inverter schematic. We will obtain the transfer characteristic curve (TCC) of inverter from DC simulation and by varying the width of the PMOS transistor; we will observe its effect on transfer characteristics.

Open Cadence Virtuoso and create a new schematic by executing, File → New → Cellview.
 Set up the 'New File' in the Command Interpreter Window (CIW)

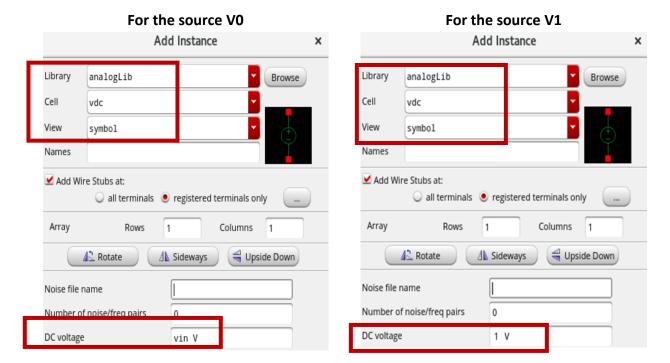
Library: *mylib*, **Cell:** *inverter2*, **View:** *schematic*, **Type:** *schematic*, **Application: Open with:** *Schematics L*



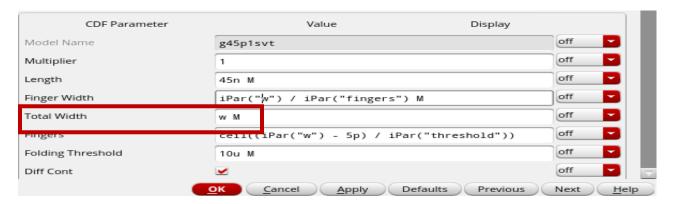


2. In the schematic window design the following schematic.

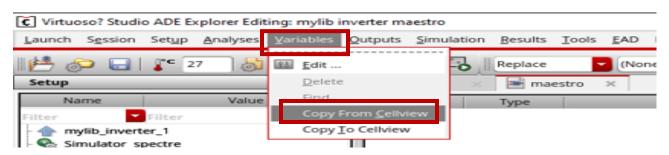
Here the **V0** and **V1** is a **vdc** type source placed from the library **analogLib**. The **V0** source is connected between 'in' and 'gnd!' and the **V1** source is connected between **source of PMOS** and **gnd**. Now, select the **V0** source and click 'q', the 'Edit object properties' window will open. Place **vin** under '**DC** voltage' field. Similarly, for the **V1** source place **1 v** as shown below.



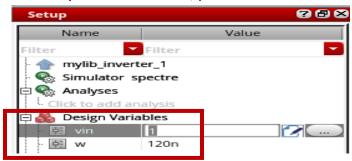
3. To sweep the width of PMOS transistor select the PMOS transistor in the schematic editor window, click 'q' and 'Edit object properties' window will open. Place w under 'Total Width' and press tab on keyboard. The 'Finger Width' field will be automatically changed as follows:



- **4.** Execute *Launch* → *ADE Explorer* and setup **Model Library** to **gpdk045_mos.scs** and section to **TT** similar to the way you did in **Lab 1**.
- **5.** Execute *Variables* → *Copy from Cellview*.



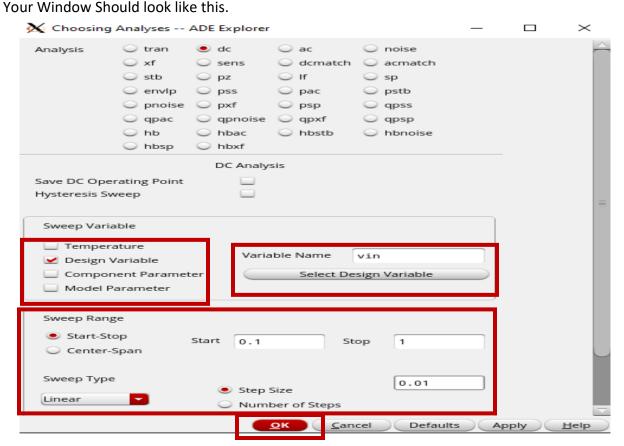
6. You will see 'w' and 'vin' appear in the 'Design Variables' window. Click on 'w' field, put a default value of **120n**.. Similarly click on 'vin' field, put a default value of **1**.



7. Execute *Analyses* → *Choose* and in the 'Choosing Analyses' form, select dc. Under 'Sweep Variable', select 'Design Variable' and click on 'Select design variable'. Select 'vin' and click OK.

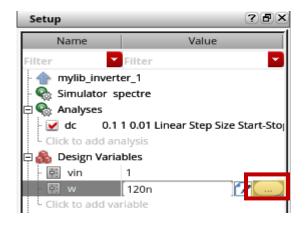


8. Under 'sweep range', select 'start-stop' and put a start value of **0.1** and a stop value of **1**. Select 'Sweep type' to be 'linear' and 'Step size' to be 0.01. Click **OK**.



- 9. Execute Outputs → To be plotted and select 'out' pin on the schematic.

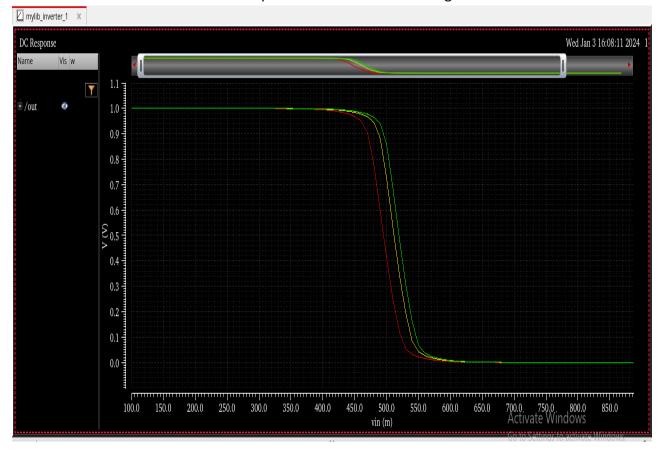
 Select Netlist and run to simulate a single TCC for the given default PMOS width of 120nm.
- 10. For Parametric Analysis, Click on, "w" under Design variable of the ADE Explorer window.



11. Click on the **3 dot icon**. The following window will appear.



12. Click on "From/To" From the drop down menu. Choose Step type as liner. Put From: 120n and To: 360n. and put Step Size: 120n. Click on Ok. Now run the simulation by executing Simulation → Netlist and Run. The output should look like following

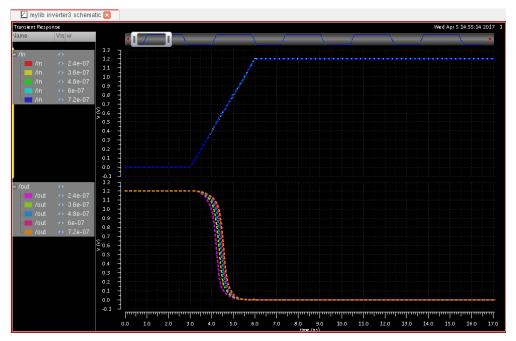


These transfer characteristics can be further explored to find Noise margin, and inversion voltage for different widths of PMOS.

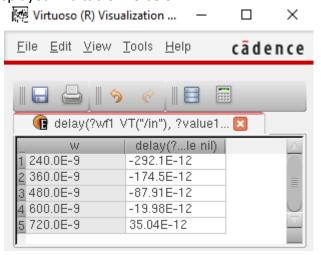
13. Save the state of the ADE Explorer window.

Student Task

- 1. Show the effect of changing NMOS width on the TCC of an inverter.
- 2. Perform a parametric analysis in transient simulation to show the effect of changing the PMOS width on the propagation delay. You are expected to obtain a similar graph as shown below:



Setup necessary settings for the **delay** function in the **waveform calculator**. Click **OK** and click on 'Evaluate the buffer and display the results in a table' icon. The results should be displayed in a table like below:



- 3. Some of the propagation delays are negative. Explain why?
- 4. Explain the change in propagation delay with the change in PMOS transistor width.
- 5. Obtain the output characteristic curve (ID vs VDS) and transfer characteristic curve (ID vs VGS) of NMOS and PMOS.

Lab-7: Custom Layout of an Inverter

Objectives:

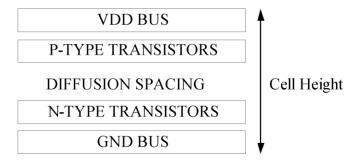
- To create a layout view of the basic inverter circuit from scratch in Virtuoso Layout Editor
- To design the layout keeping basic design rules in mind
- To design cell layout of a constant height for use in hierarchical design

Introduction to Layout, DRC and LVS

Layout is representation of a circuit in terms of planar geometric shapes (e.g. rectangles, polygons) showing the patterns of metal, polysilicon, oxide, or diffusion layers that make up the components (resistors, inductors, capacitors, transistors) of the integrated circuit.

When using a standard process (e.g. 45nm, 90nm or 180nm process available in our lab), the behaviour of the final integrated circuit depends significantly on the positions and interconnections of the geometric shapes due to parasitic resistances and capacitances contributed by them. While designing a layout, designer must keep in mind performance (e.g. power-delay product) and size (area occupied by the chip) criterion.

While designing digital circuits, one usually follows an ASIC design flow, where, the height of standard cells that are used is the same throughout the cell library, but their widths must vary according to their logical functions and drive strengths. The following figure shows a generalized standard cell height concept:



Although we will follow a full-custom IC design flow, we will maintain same cell height throughout our cell library.

The generated layout must pass a series of checks in a process known as physical verification. The most common checks in this verification process are:

- Design Rule Checking (DRC)
- Layout Versus Schematic (LVS) checking
- Parasitic extraction and post-layout simulation

Design Rule Check (DRC):

Design Rule Checking (DRC) is the process that determines whether the designed layout of a circuit satisfies a rules specified by the process being used.

Design Rules are a series of rules (e.g. area, width, overlap, enclosure, extension, spacing) provided by semiconductor manufacturers which are specific to a particular semiconductor manufacturing process. Design rules specify certain geometric and connectivity restrictions to ensure that the process can fabricate the device properly.

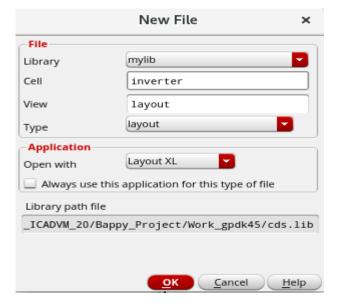
Layout versus Schematic (LVS) Check:

The Layout Versus Schematic (LVS) is the verification step to determine whether a particular integrated circuit layout corresponds to the original schematic or circuit diagram of the design. A successful Design rule check (DRC) ensures that the layout conforms to the rules designed/required for faultless fabrication. However, it does not guarantee if it really represents the circuit we desire to fabricate. This is why an LVS check is used.

Layout design using Virtuoso Layout Suite XL Editor

1. Invoke **Virtuoso Layout Suite XL Editor** from the **CIW** by executing **File New Cellview**. The **New File** form appears. Fill it in as shown in the figure below:

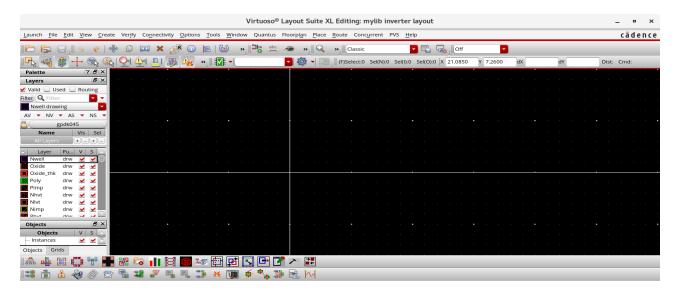
Cell: inverter, View: layout. Click OK.



2. Click 'Always' if the following window appears before Layout window appears.



The following window of Virtuoso Layout Suite XL Editor will appear.



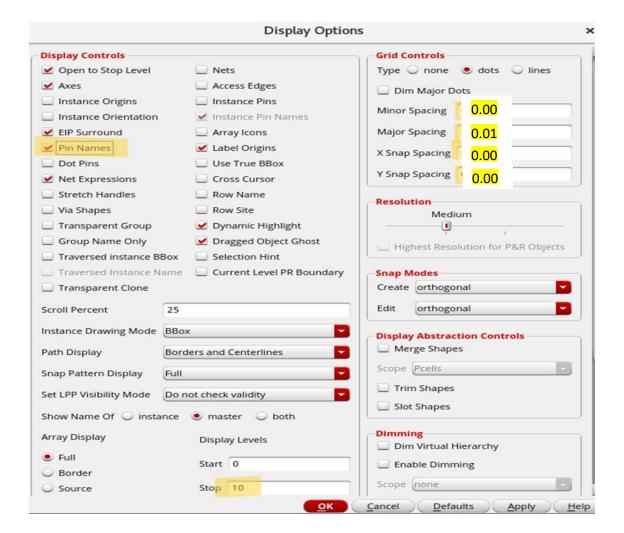
On the left side of the window, you will find a panel called 'Layers'. This panel is divided in three main categories which are: layer color, layer name and layer purpose. The details are described in the table below:

Color	Matches the color in the Editing window. Each layer has its own color and pattern. Each layer has two colors associated with it: a fill color and an outline color. These colors can be changed to fit your taste by editing the technology file.
Name	The type of layer (Nwell, Oxide, Poly, Metal1, etc)
Purpose	In gpdk045 the only purpose classifications are: drw = drawing, slot = slot Drawing is used in layout, slot is used to create a hole for metal stress relief

Verify that the layers display corresponds to the gpdk045layers shown in the GPDK 90 nm Mixed Signal Process Specification manual.

3. Before starting to design layout, you need to set the layout display configuration. Execute the following in the Virtuoso Layout Editor: *Options Display* or press 'e' on keyboard. Configure the form as shown in the figure below: You have to set the following parameters only:

Minor spacing	0.001
Major spacing	0.01
X snap spacing	0.005
Y snap spacing	0.005
Display Levels: Stop	10



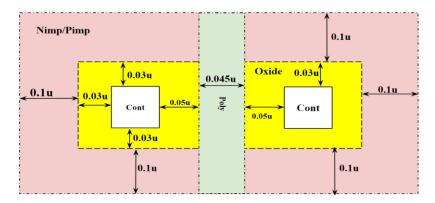
4. Now we are going to build the layout of the inverter. An inverter has an NMOS and a PMOS transistor. First we will build an NMOS transistor.

Layout of NMOS inverter consists of oxide, Nimp, Cont and Poly layers. Study the rules of these layers and calculate the minimum size of the Poly, Cont, Oxide and Nimp layer to create an NMOS transistor.

The rules related to the NMOS transistor of	can be summarised as follows:
---	-------------------------------

Contact size	$0.06 \mu \text{m} \times 0.06 \mu \text{m}$ (Fixed)	
Poly width (Minimum)	0.045 μm (Fixed MOS gate length)	
Contact to poly spacing (Minimum)	0.05 μm	
Contact to oxide enclosure (Minimum)	0.03 μm	
Poly/Nimp extending from oxide (Minimum)	0.1 μm (gate side enclosure)	
Nimpenclosing oxide (Minimum)	0.1μm (enclosure other than gate sides)	
Minimum Metal 1 width	0.06 μm	
Maximum Metal 1 width	6 μm	
Minimum Metal 1 to Contact enclosure	$0.03 \mu \text{m}$ (on at least two opposite sides)	

The following figure illustrates some of the design rules mentioned above:



Now study the PMOS transistor structure in the GPDK 45 nm Mixed Signal Process Spec. The PMOS transistor consists of Oxide, Poly, Pimp, Cont and Nwell layer. Study the rules of these layers and calculate the minimum size of Poly, Cont, Oxide, Pimp and Nwell layer to create a PMOS transistor. The rules related to PMOS are same as NMOS except the there is an additional layer, the Nwell, whose rules are as follows:

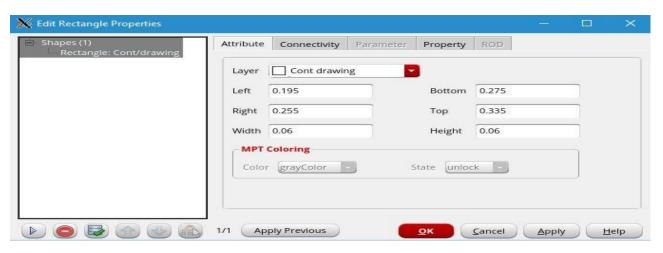
Minimum Nwell width	0.3μm
Minimum Nwell spacing to Nwell (same potential)	0.3 μm
Minimum Nwell spacing to Nwell (different potential)	0.6 <mark>μ</mark> m
Minimum Nwell spacing to N+ active area	0.16 μm
Minimum Nwell spacing to P+ active area	0.16 μm
Minimum Nwell enclosure to P+ active area	0.06 μm
Minimum Nwell enclosure to N+ active area	0.06 μm
Minimum N+ Active Area to P+ Active Area Spacing	0.1 <mark>μ</mark> m

Now we start building the NMOS and PMOS transistor layout. Look at the **LSW** and find the current drawing layer.

5. Click on the following icon in **Virtuoso Layout Suite XL Editor** window so that it notifies you anytime you make a violation of any design rule. When clicked, it will show '**DRD Notify ON**'. DRD stands for Design Rule Driven.

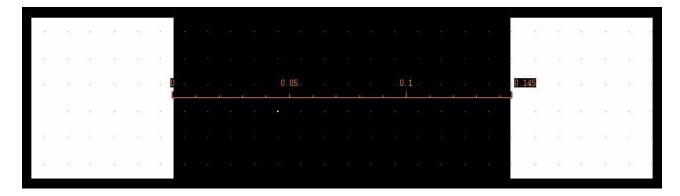


6. Select 'Cont (drw)' (contact) layer from the 'Layers' panel and draw a rectangle of 'Cont (drw)' layer using *Create* Shape Rectangle or simple pressing 'r'. Press 'Esc' to stop 'create rectangle' tool. In gpdk045 technology, Cont layers must be of dimension **0.06** μm x **0.06** μm. So, if your rectangle is not of that dimension, click on the rectangle, press 'q'. In the following window, check if the criterion has been met and change 'Width/Height' if required.



Contact to poly spacing must be 0.05 μ m in this technology and the channel length of NMOS/PMOS in our design is 0.045 μ m. So, we need a minimum space of 0.145 μ m between the contacts at source and drain.

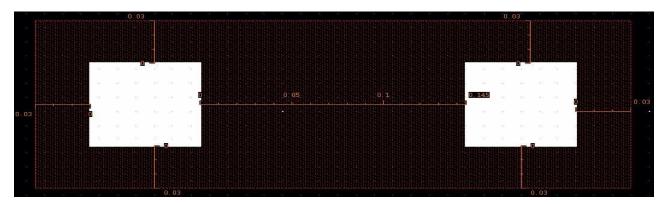
7. Press 'k' to invoke the 'ruler' tool. Use it to measure lengths whenever needed. To copy, press 'c'. After placing two contacts, the layout looks like this:



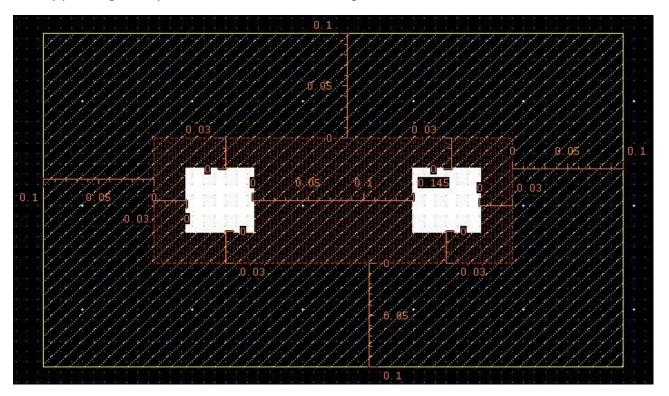
8. Now, **contact to oxide spacing** is minimum **0.03** μ m. So, draw a rectangle of 'Oxide (drw)' layer so that it covers both the contacts and extends from each side by **0.03** μ m.

While drawing this, you will see Design rule violations when they are committed.

9. After drawing oxide layer, the layout should look like this:

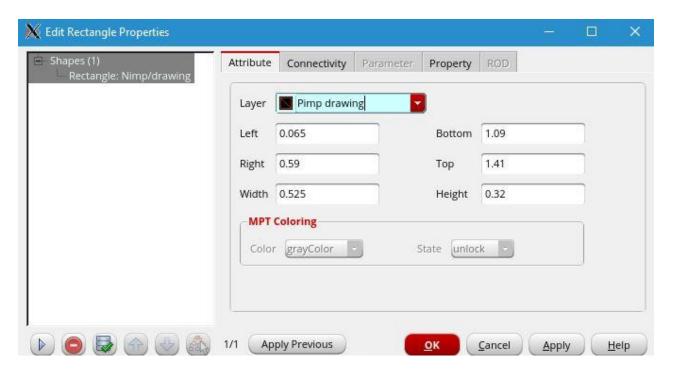


10. Now we will draw 'Nimp (drw)' layer, which must extend from the oxide layer by a minimum of **0.1** μ m. First, draw a rectangle and then extend it to meet design rules. Use stretch tool by pressing 's'. Layout will look like the following:



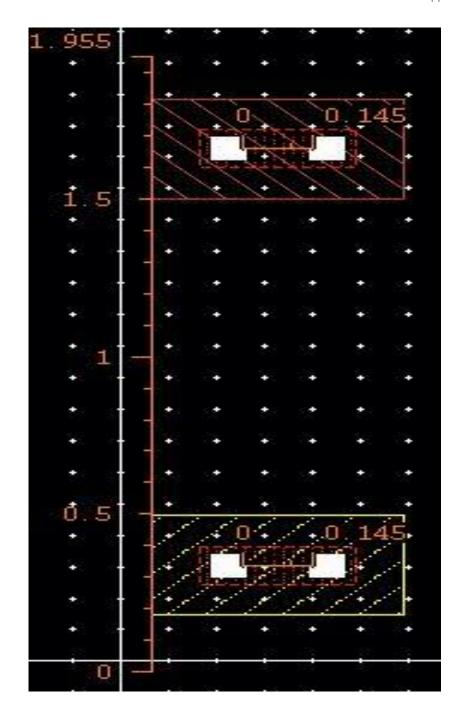
11. Now, copy it and create another copy of all these layers by selecting all and pressing 'c'.

12. Click on the 'Nimp (drw)' layer of the copy in the upper portion of the layout and press 'q' to edit properties. From 'Edit Rectangle Properties' window, select 'Pimp (drw)' layer under 'Layer' option. Click **OK**.

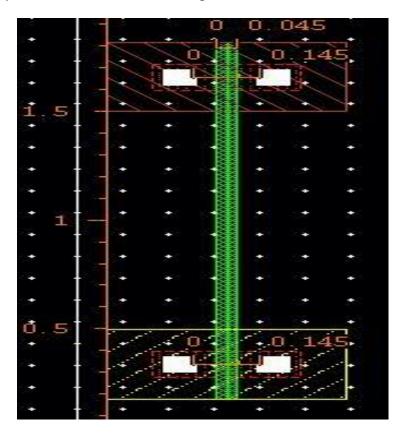


13. With more metal layers available in today's silicon processes, using the routing approach, such as first metal traverse vertically and second metal traverse horizontally, would be advantageous in standar cell physical design. Using this method, the second layer (e.g. Metal2) can be used for power and ground routing over internal standard cell transistors. In standard cell layout, it is preferable to use firt conducting layer, such as Metal1, as much as possible to make internal connections of NMOS and PMOS transitors within the cell. If there is a nedd to use other conducting layers, such as, Metal2, use of such layers must be kept to a minimum. It is desired to use first routing (e.g. Metal1) layer for standard cell ports.

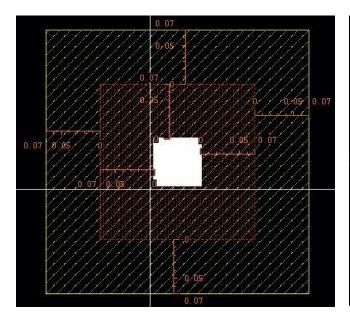
Our cells will have a height of $0.32 \, \mu m$. Place the two parts (NMOS and PMOS) $1 \, \mu m$ apart, and create a ruler so that the cell height can be checked whenever needed and the separation between the NMOS and PMOS can be maintained properly. Now, the layout will look like the following:

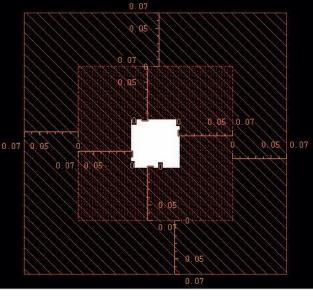


14. Next, draw a 'Poly (drw)' path by selecting 'Poly' layer from the 'Layers' panel and pressing 'p' to invoke 'create path' tool. This layer must be of **0.045** μ m in width and in between the two contacts, extending from the oxide layer by **0.1** μ m (at least, on both sides). After placing the 'poly' gate, the layout will look like the following one:

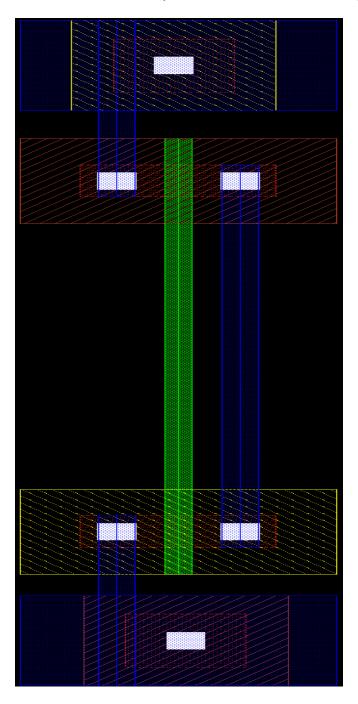


15. Now that you know most of the shortcuts and layers, draw contact for body terminals for NMOS and PMOS. These portions should consist of Cont, Oxide and Nimp (for body of PMOS) or Pimp (for body of NMOS). Check DRD notifications for design rule violations. The following figure shows a Psubstrate and an Nwell contact.





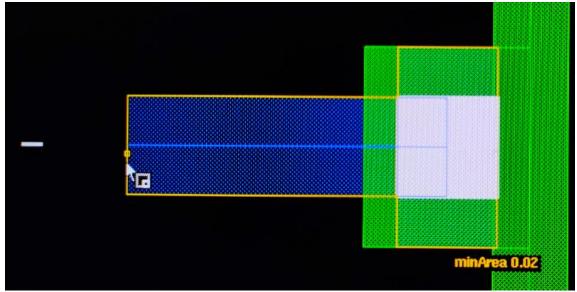
- **16.** Connect the Drain regions of the NMOS and PMOS. Also connect the source of both MOS's to respective body terminals using 'Metal1 (drw)' layer. Connect the drains of the MOS's using 'Metal1 (drw)' layer.
- **17.** PMOS should be in 'Nwell (drw)'. So draw an 'Nwell (drw)' rectangle surrounding both the PMOS and the body contact for PMOS. The layout will look like the following:



18. Now, we have to place pins. The gate is in 'poly (drw)' layer. Let's bring it to 'Metal1(drw)' layer by extending the 'Poly (drw)' layer, creating a contact between 'Poly' and 'Metal1' layer by pressing 'o' to 'create via' and selecting 'M1_POv' under 'via definition' and placing it on layout.

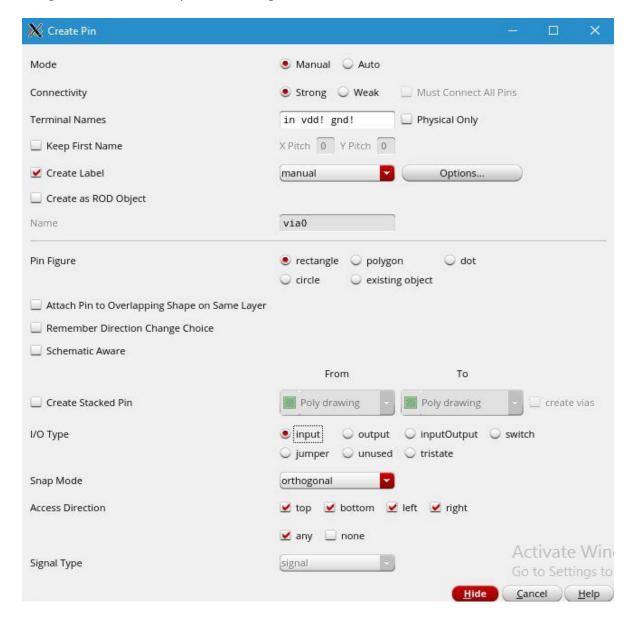


19. Also draw a 'Metal1 (drw)' rectangle on the via, because the default Metal1 rectangle area is less than the required minimum.



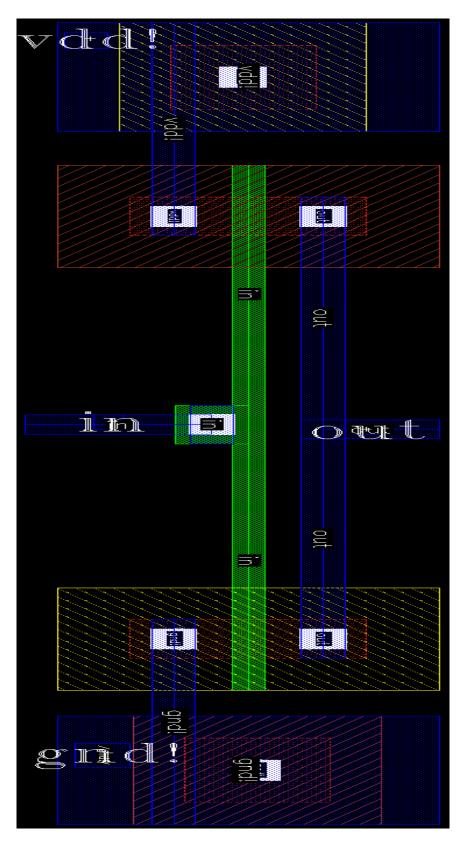
20. Now, Execute *Create* Pin to create pins for vdd!, gnd!, in and out.

For in, vdd! and gnd! select 'input' as 'I/O type' and for out select 'output' as 'I/O type'. Now, draw rectangles on the Poly-Metal1 via for 'in' pin, PMOS source-to-body 'Metal1' connection for 'vdd!' pin and NMOS source-to-body connection for 'gnd!' pin. For 'out' pin, draw the rectangle on the Metal1 layer connecting the two drains of MOS's.



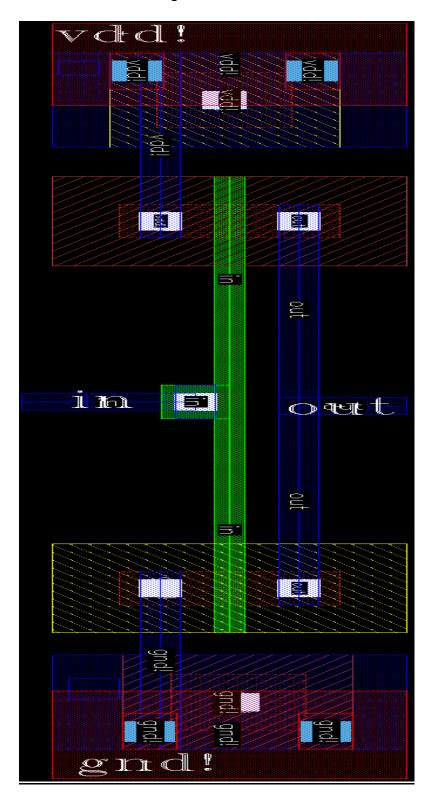
You may add label to pins.

Your Layout will look like this.



21. Finally, add **Metal2** paths of **0.5** μ width for power rails and connect them to power nets in **Metal1** by using **Metal1** to **Metal2** via by invoking 'create via'.

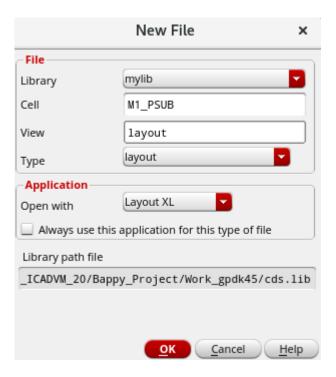
The final layout will look like the following:



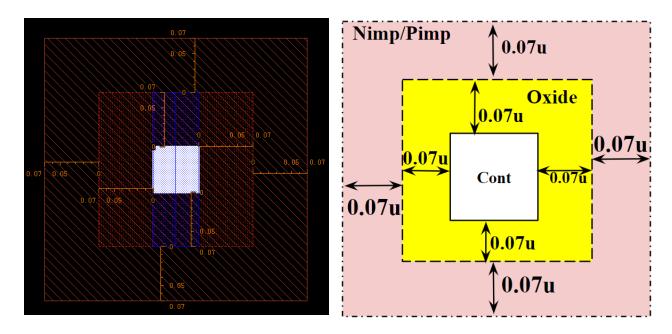
Creating Body ties

Now you know what body tie is. We will now make two instances for body ties one for **Psub** and one for **Nwell**.

1. Execute File New Cellview and fill in the New File form as follows. Click OK.



2. Draw psubstrate contact in the same way as you have made it in Lab3.



3. Save it and make nwell contact similarly (name it **M1_NWELL**), just change the **Pimp** layer to **Nimp** and everything else is the same.

Save these two for later use.

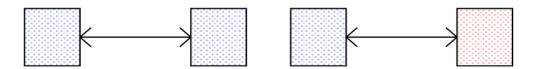
Appendix A (Shortcut keys for Cadence Virtuoso ® Layout Editor L)

Shortcut Key	Tasks performed	
f	Fit display to window	
r	Draw rectangle	
q	Edit property of an object	
р	Makes a min width path of the layer	
	selected in LSW	
Ctrl+a	Select all	
Ctrl+d	Deselect all	
С	Сору	
m	Move	
S	Stretch side of a rectangle	
k	Invoke ruler tool	
Shift+k	Delete all rulers	
i	Add an instance	
u	Undo	
Shift+u	Redo	
е	Display options	
0	Add via between layers	
I	Create a label	

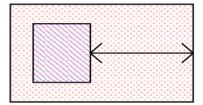
Appendix B (gpdk090 Design Rules Guide (Abridged Version for VLSI-I Lab))

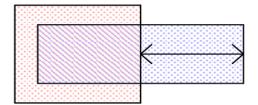
Terminology Definitions

Spacing - distance from the outside of the edge of a shape to the outside of theedge of another shape.

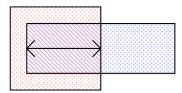


Enclosure - distance from the inside of the edge of a shape to the outside of theedge of another shape.





Overlap - distance from the inside of the edge of a shape to the inside of the edgeof another shape.



Butting - outside of the edge of a shape touching the outside of the edge of anothershape.



Lab-8: Post Layout Verification

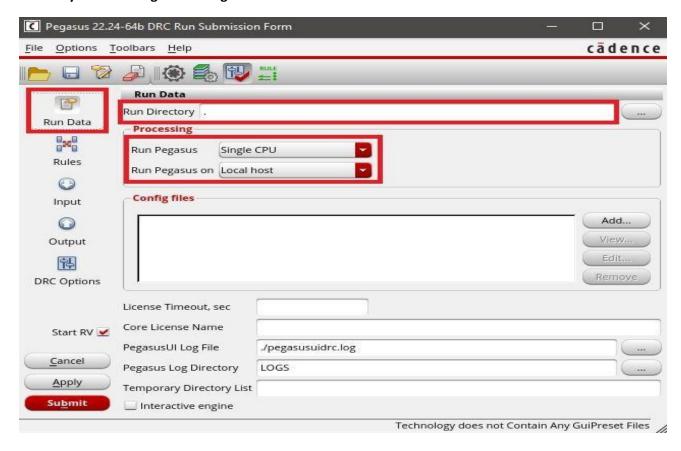
Objectives:

- To perform Design rules check (DRC), Layout vs. Schematic check (LVS) of inverter layout
- To extract parasitic resistance and capacitance from layout of designed inverter
- To perform transient simulation of extracted view
- To create layout views for body ties of NMOS and PMOS for further use

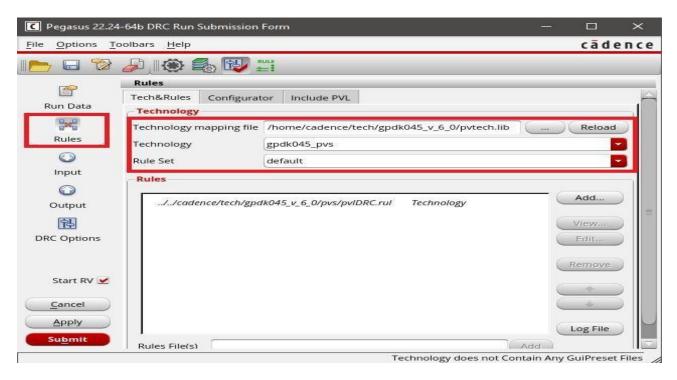
Design Rule Check (DRC)

1. Now we would like to check the DRC rules by Pegasus. Execute Pegasus 2 DRC

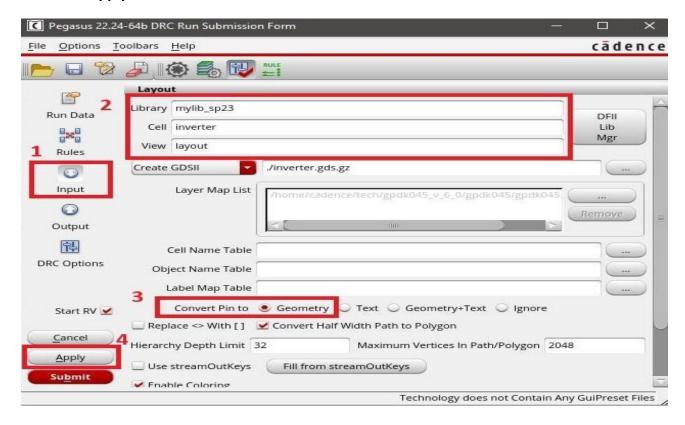
The following **DRC Run Submission Form** will appear. In the **Run Data** section, put dot(.) in the **Run Directory** and **Run Pegasus** in **Single CPU** and on **Local host** as shown below.



2. Now in the **Rules** section select the **Technology mapping file**, **Technology** and **Rule Set** as shown below.



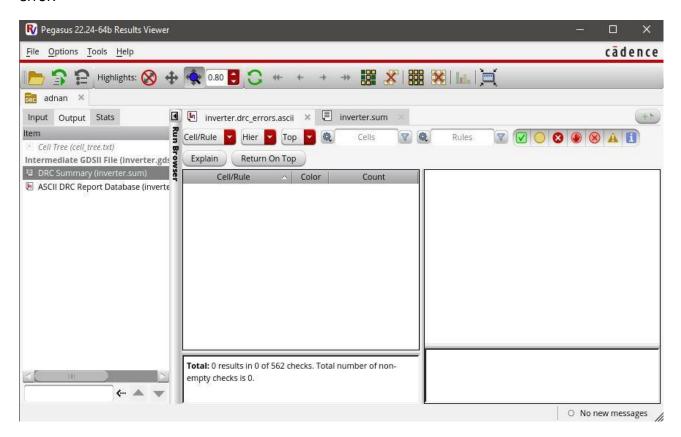
4. In the Input section select your **Library, Cell,** and **View**. Also, select **Convert Pin to Geometry.** Then click **Apply.**



5. Click **Yes** if the following window appears.

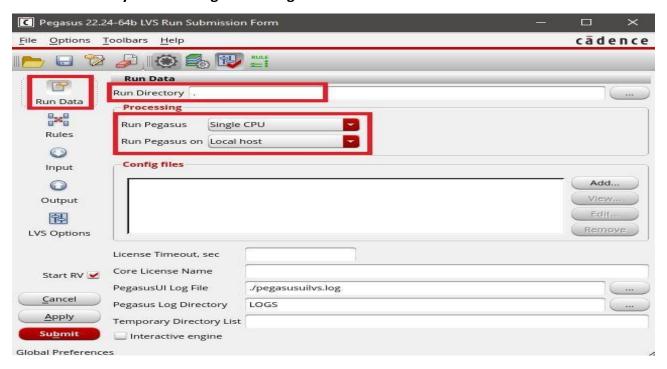


6. The following **Results Viewer** will appear. The **DRC Summary** will be empty if there is no error.

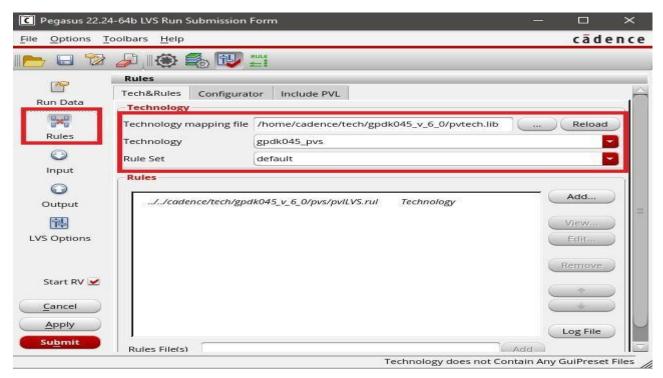


Layout Versus Schematic

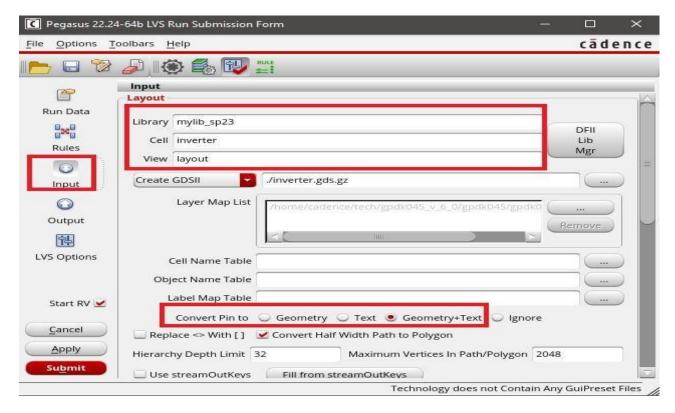
- 1. Execute **Pegasus** → LVS
- 2. The following LVS Run Submission Form will appear. In the Run Data section put dot (.) in the Run Directory and Run Pegasus in Single CPU and on Local host as shown below.



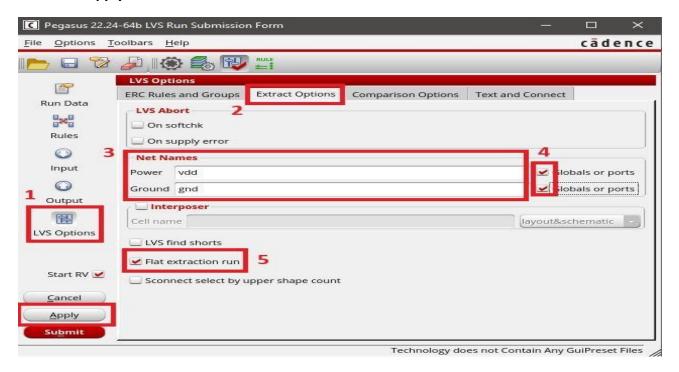
3. Now in the **Rules** section select the Technology mapping file, Technology and Rule Set as shown below.



4. In the Input section select your **Library, Cell,** and **View**. Also, select **Convert Pin to Geometry+Text**.



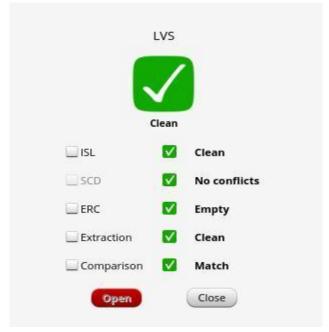
5. Now in the **LVS Options** section, go to the **Extract Options** tab write the **Net Names** as shown below and **select** the **global or ports** option and **Flat extraction run** as shown below. Then click **Apply.**



6. Click **Yes** if the following window appears.



7. If the layout matches with schematic the following window will appear.



Lab-9: Schematic Driven Layout Design

Objectives:

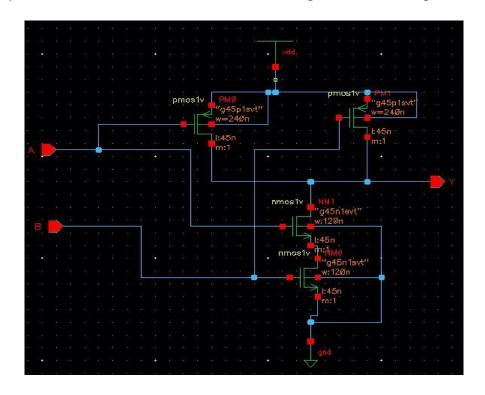
- To be familiar with schematic-driven layout with the example of a 2-input NAND gate.
- To perform Schematic Level Verification, Layout Design, DRC and LVS check and perform post-layout simulation from extracted view.

Creating Layout using Virtuoso Layout Editor XL

- **1.** Virtuoso Layout Editor XL is a schematic-driven layout generation tool. To learn schematic driven layout, we will create the schematic view of a 2-input NAND gate cell which we named *NAND2X1*.
- 2. Instantiate the following cells to your schematic.

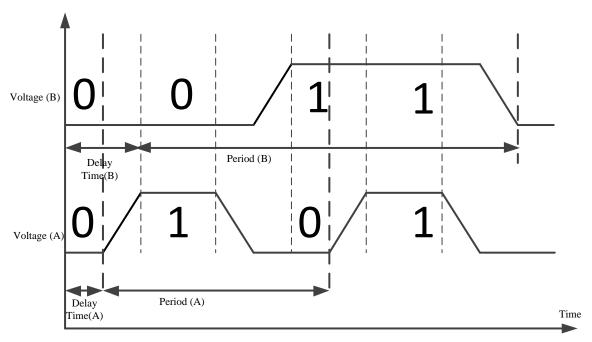
Library Name	Cell Name	Properties/Comment
gpdk090	nmos1v	For NM0 and NM1, Width = 240n
gpdk090	pmos1v	For PM0 and PM1, Width = 480n
analogLib	vdd	
analogLib	gnd	

Use your experience from Lab1 to draw the schematic diagram of the nand gate.

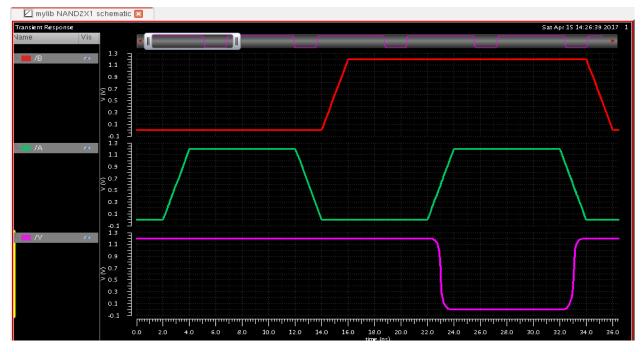


3. Launch **ADE L** and simulate the design to verify its functionality. Setup **Model library**, **Analysis** type and **Outputs to be plotted** as you have done in previous lab.

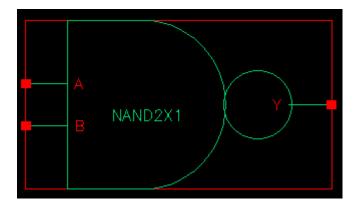
While setting inputs for signals A and B, you have to use different periods and delays for the two signals, so that you can observe all four cases (00, 01, 10, 11) of input signals. Also make sure $0\rightarrow 1$ and/or $1\rightarrow 0$ transitions for both input signals do not occur at the same time. The following figure shows a sample of two signals meeting these criteria:



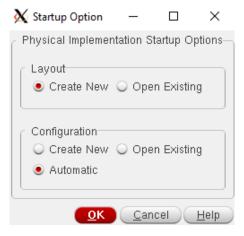
A sample waveform window would look like the following after simulation:



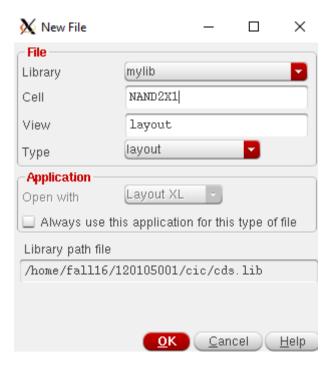
4. Then create a symbol in the same way you have made symbol of inverter in lab2. Make it look like a nand gate.



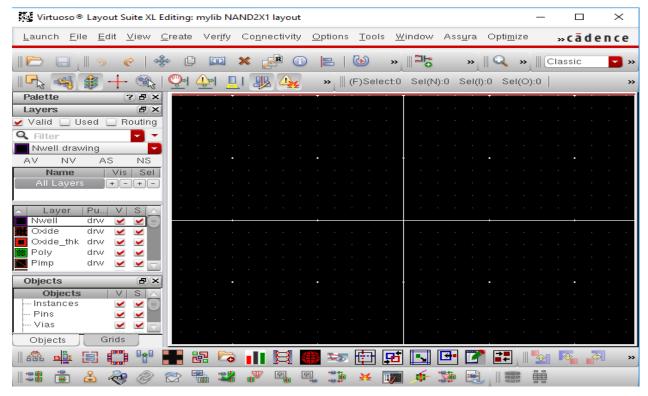
5. In schematic editor window, execute: *Launch → Layout XL*. The following window will appear:



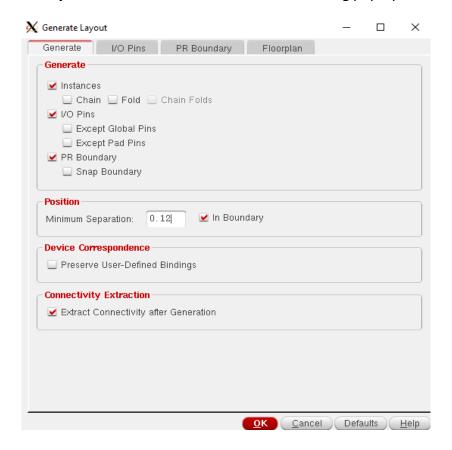
6. Click OK. 'New File' window for layout will appear. Click OK.

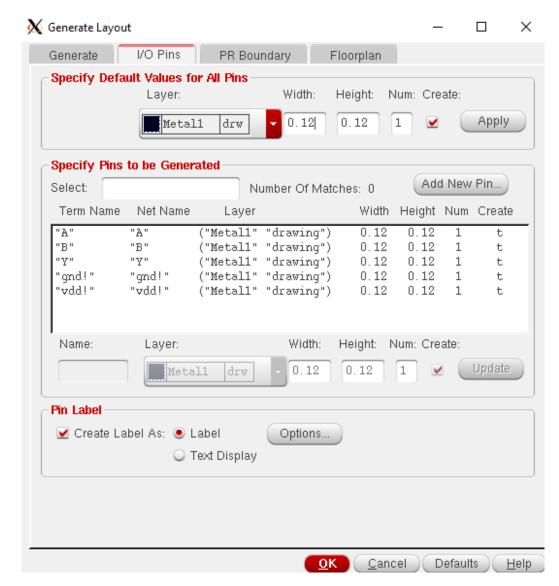


'Virtuoso Layout Editor XL' window will appear.



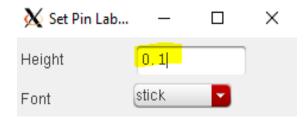
7. Execute Connectivity -> Generate All From Source. The following pop-up window will appear:



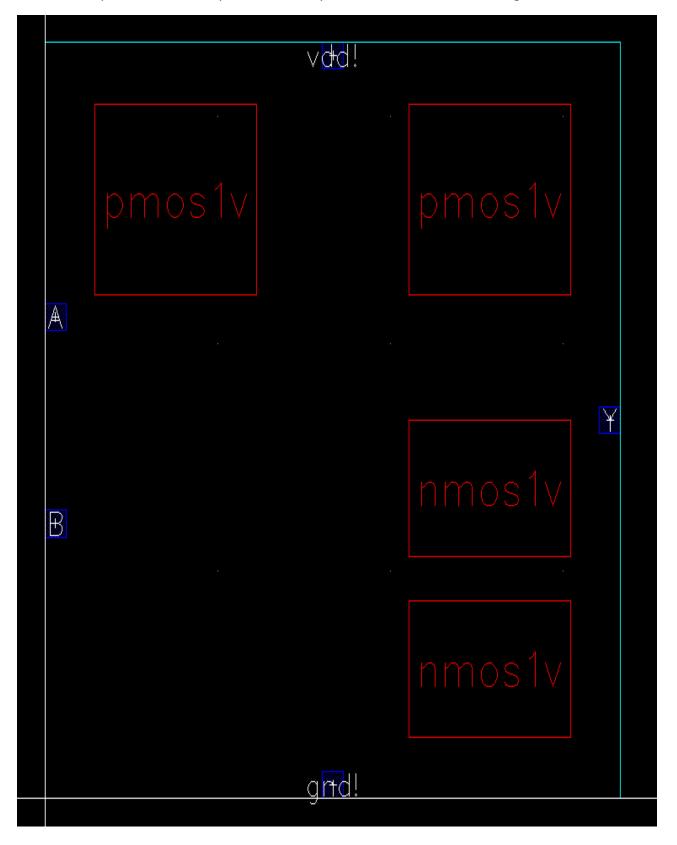


8. Go to **I/O pins** tab. The dialog box shows that all I/O pins are in **Metal1** layer (**Metal1 drw**).

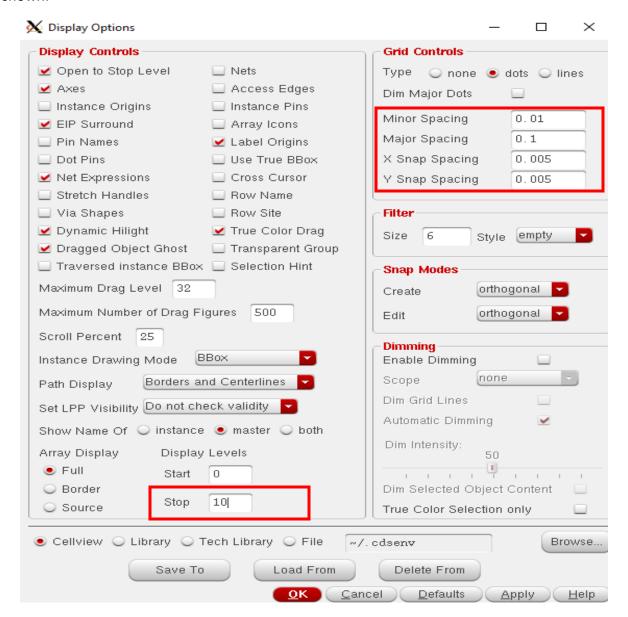
Also put a tick mark on **Create label as Label** and click on **Options**. The following **Set Pin Label** window will appear. Set **Height** to 0.1. Then click **OK** on both the windows.



9. The initial pin and transistor placement in layout will look like the following:



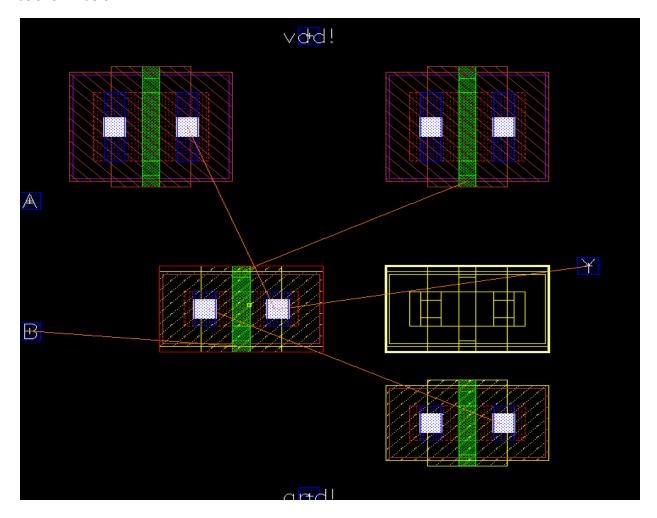
10. Execute *Options* → *Display* or Press 'e' on keyboard to open 'Display Options'. Fill it in as shown:



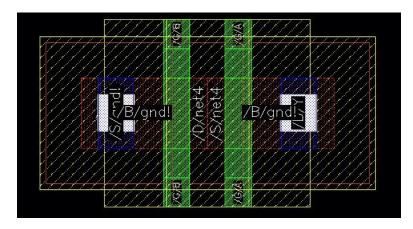
11. The transistors and pins are shown inside a bounding box, which is an estimate of the optimum size of the final layout. Automatic router will use the bounding box to constrain all routing to occur within the box. The bounding box may need to be re-sized to accommodate all components. An important concept to keep in mind during resizing is that standard cells typically have fixed height (so that power/ground rails line up correctly for routing purposes). **Delete** the **PR Boundary** for now.

Virtuoso Layout Editor XL (VXL) and gpdk090 allow us to create stacked transistors with shared source/drain areas. Zoom in to two transistors at the bottom (to zoom in, type "z" and draw a box around the transistors). Click on the transistor on the right and type "m" to move the

object. As you start dragging the object to the left, fly-lines indicating connectivity will appear as shown below:

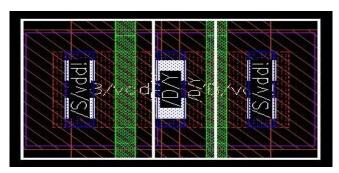


12. When the source/drain areas are overlapped, left-click to fix the position. You should see a transistor stack with shared source/drain areas like this (depending on how far you move, you may need to move left/right a bit):



This is a nice NMOS stack for the NAND gate. As you can see, the source/drain contacts have disappeared. Back to the big picture, zoom to fit (press "F").

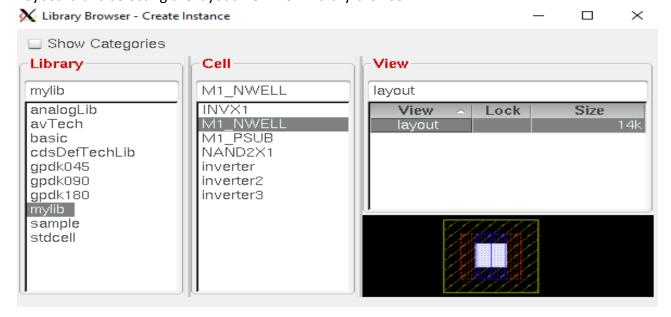
Let's do the same exercise for the PMOS transistors. The PMOS transistors in nand gate do have shared drain contacts because they work in parallel. Connectivity information is extracted from schematic by VXL. The pull-up network looks like the following:



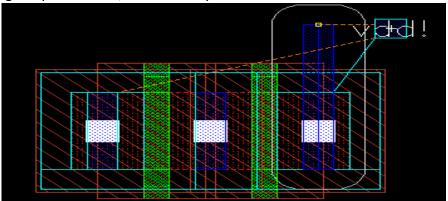
13. Now, connect different layers using path tool (press 'p' on keyboard), and fill areas by drawing rectangles where necessary (press 'r' on keyboard). To connect one layer to another (e.g. **Poly to Metal1** or **Metal1 to Metal2**), create via by pressing 'o' on keyboard and selecting proper 'Via Defintion'.



14. Instantiate **M1_PSUB** and **M1_NWELL** cells (that you have created earlier) by pressing 'i' on keyboard and selecting the layout view from library browser.

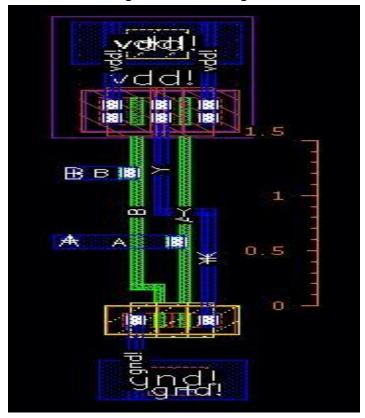


15. Wire up the layout. When you do so, you may encounter multiple options for certain pins. For example, when you select the PMOS to connect its source to VDD, there are multiple Metal1 wires in the PMOS. The desired path will be highlighted and you'll see the fly-line. Continue until you finish routing all the signals. Move **vdd!** and **gnd!** pins to the power rails. As you are moving the pins around, notice the fly-lines that indicate the connections.



A practice that you can follow while wiring is to use **Metal1** for all vertical wiring and **Metal2** for all horizontal wiring inside the cell. Also make the cell height $5 \mu m$.

16. Your final layout will look something like the following:



17. Perform DRC, LVS and QRC for NAND2X1 as you have done in previous labs. Generate **av_extracted** view and simulate the circuit from that view to verify the functionality.

Lab-10: Introduction to Hierarchical Layout Design

Objectives:

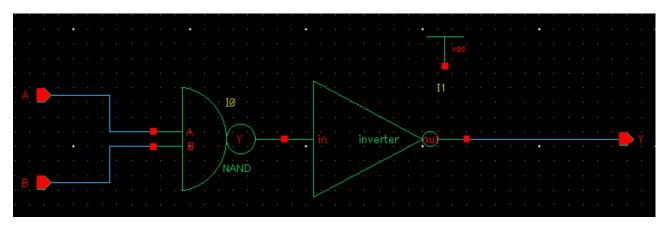
- To be familiar with concept of hierarchical design
- To perform Schematic Level Verification, Layout Design, DRC and LVS check
- To perform post-layout simulation of top level design

Introduction to Hierarchical Design

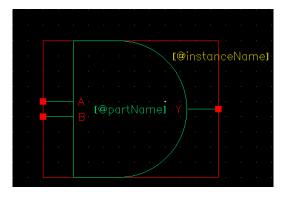
By this time, you should have completed layout of *INVX1* and *NAND2X1*. Now, you will learn how to perform hierarchical design. (cell *INVX1* in this section is **inverter** in your case)

- **1.** Create a new **cellview** of type schematic named *AND*.
- 2. Instantiate NAND and INVERTER symbol from your library mylib in that schematic.

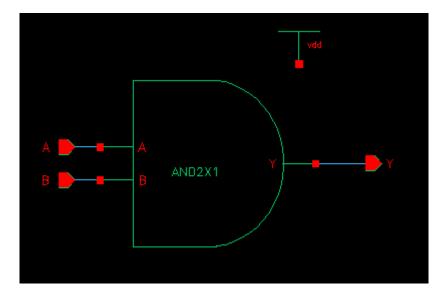
Your final schematic should look something like the following:



3. Now make a symbol of AND.



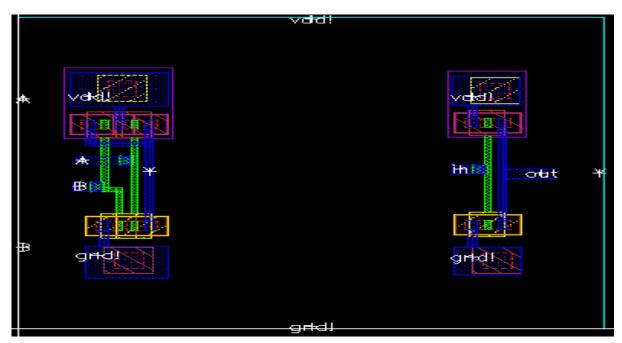
4. Now create a new **cellview** named *AND_test*, instantiate *AND* and *vdd* in that cell and the final schematic should look like the following:



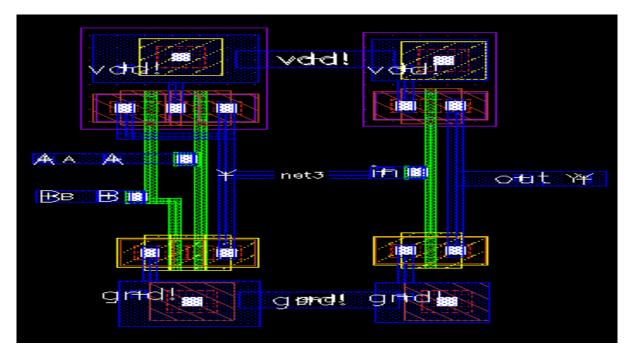
5. Now, launch **ADE L**, setup **Stimuli**, **Model library**, **Analysis** type and **Outputs to be plotted** in the same way as you have done in Lab 5. Run the simulation.



- **6.** If functional verification is okay, then execute *Launch → Layout XL* from the schematic of **AND2X1**.
- **7.** Follow procedure of Lab 5 to generate instances and set display options. You will get something like the following:



8. Connect them as required and the final layout should look like the following (probably better!)



9. Perform DRC, LVS and QRC as you have done in previous labs.

References and Acknowledgment

The following resources have been consulted while preparing the manual.

- "Fundamentals of Digital Logic with Verilog Design" by Stephen Brown and Zvonko Vranesic
- "CMOS VLSI Design: A Circuits and Systems Perspective" by Neil Weste, David Harris.
- "Physical Design Essentials: An ASIC Design Implementation Perspective" by Khosrow Golshan.
- "Digital VLSI Chip Design with Cadence and Synopsys CAD tools" by Erik Brunvand.
- "Custom IC Design Manual" provided by University Support Team, Cadence® Design Systems, Bangalore, India

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